Datasheet

MM32SPIN05x

32-bit Micro controller based on ARM Cortex M0

Ver: 1.09_q

Content

1	intro	auctio		1
	1.1	Descri	ption	1
	1.2	Produc	ct Features	1
2	Spe	cificatio	on	3
	2.1	Device	contrast	3
	2.2	Summ	ary	3
		2.2.1	ARM® Cortex TM -M0 and SRAM	3
		2.2.2	Memory	4
		2.2.3	SRAM	4
		2.2.4	Clocks and startup	4
		2.2.5	Nested vectored interrupt controller (NVIC)	4
		2.2.6	Extended interrupt/event controller (EXTI)	5
		2.2.7	Boot modes	5
		2.2.8	Power supply schemes	5
		2.2.9	Power supply supervisors	5
		2.2.10	Voltage regulator	5
		2.2.11	Low-power modes	5
		2.2.12	Direct memory access controller (DMA)	6
		2.2.13	Timers and watchdogs	6
		2.2.14	Universal asynchronous receiver/transmitter (UART)	9
		2.2.15	I2C interface	9
		2.2.16	Serial peripheral interface (SPI)	9
		2.2.17	General-purpose inputs/outputs (GPIO)	9
		2.2.18	Analog-to-digital converter (ADC)	9
		2.2.19	Hardware Dvision	10
		2.2.20	Temperature sensor	10
		2.2.21	Serial single line SWD debug port (SW-DP)	10
		2.2.22	Comparator (COMP)	10
3	Pin	definitio	on	13
4	Men	nory ma	apping	23
5	Flec	trical c	haracteristics	25
•	5.1		eter conditions	
	0.1	5.1.1	Minimum and maximum values	
		5.1.2	Typical values	
		5.1.3	Typical curves	
		5.1.4	Loading capacitor	
		5.1.4		
		5.1.5	Pin input voltage	
		5.1.7	• • •	
	5 2		Current consumption measurement	
	5.2		Ite maximum ratings	
	5.3	Opera	ting conditions	Z Ø

		5.3.2	Operating conditions at power-up/power-down	29
		5.3.3	Embedded reset and power control block characteristics	29
		5.3.4	Supply current characteristics	30
		5.3.5	External clock source characteristics	34
		5.3.6	Internal clock source characteristics	36
		5.3.7	Memory characteristics	37
		5.3.8	EMC characteristics	38
		5.3.9	Absolute Maximum (Electrical Sensitivity)	39
		5.3.10	I/O port characteristics	40
		5.3.11	NRST pin characteristics	43
		5.3.12	Timer characteristics	44
		5.3.13	Communication interfaces	45
		5.3.14	12-bit ADC characteristics	50
		5.3.15	Temperature sensor characteristics	54
		5.3.16	Comparator characteristics	54
6	Pacl	kage inf	formation	56
	6.1	LQFP4	8 Package information	56
	6.2	LQFP3	2 Package information	58
	6.3	QFN32	Package information	60
	6.4	QFN20	Package information	62
	6.5	TSSOF	P20 Package information	64
7	Orde	ering in	formation	66
R	Revi	ision hi	story	67

List of Figures

1	Block diagram	11
2	Clock tree	12
3	LQFP48 packet pinout	13
4	LQFP32 packet pinout	14
5	QFN32 packet pinout	15
6	QFN20 packet pinout	15
7	TSSOP20 packet pinout	16
8	Pin loading conditions	25
9	Pin input voltage	26
10	Power supply scheme	26
11	Current consumption measurement scheme	27
12	Typical current consumption in standby mode vs. temperature at V_{DD} = 3.3 V	31
13	Typical current consumption in stop mode vs. temperature at V_{DD} = 3.3 V	32
14	High-speed external clock source AC timing diagram	34
15	Typical application with an 8 MHz crystal	36
16	I/O AC characteristics	43
17	Recommended NRST pin protection	44
18	I2C bus AC waveform and measurement $circuit^{(1)}$	46
19	SPI timing diagram-slave mode and CPHA = 0	
20	SPI timing diagram-slave mode and CPHA = 1 ⁽¹⁾	49
21	SPI timing diagram-master $mode^{(1)}$	50
22	Typical connection diagram using the ADC	53
23	Power supply and reference power supply decoupling circuit	54
24	LQFP48 - 48-pin low-profile quad flat package outline	56
25	LQFP32 - 32-pin low-profile quad flat package outline	58
26	QFN32 - 32-pin quad flat no-leads package outline	60
27	QFN20 - 20-pin quad flat no-leads package outline	62
28	TSSOP20 - 20-lead thin shrink small outline package outline	64
29	Ordering information scheme	66

List of Tables

1	MM32SPIN05x device features and peripheral counts	3
2	Timer feature comparison	6
3	Pin definitions	16
4	Alternate functions for port A	21
5	Alternate functions for port B	22
6	Alternate functions for port C	22
7	Alternate functions for port D	22
8	Memory mapping	23
9	Voltage characteristics	27
10	Current characteristics	27
11	Thermal characteristics	28
12	General operating conditions	28
13	Operating conditions at power-up/power-down	29
14	Embedded reset and power control block characteristics	29
15	Typical and maximum current consumption in stop and standby modes $^{(2)}$	31
16	Typical current consumption in Run mode, code executing from Flash	32
17	Typical current consumption in sleep mode, code executing from Flash or RAM	33
18	On-chip peripheral current consumption $^{(1)}$	33
19	High-speed external user clock characteristics	34
20	HSE oscillator characteristics ⁽¹⁾⁽²⁾	35
21	HSI oscillator characteristics ⁽¹⁾⁽²⁾	
22	LSI oscillator characteristics ⁽¹⁾	36
23	Low-power mode wakeup timings	37
24	Flash memory characteristics	37
25	Flash memory endurance and data retention $^{(1)(2)}$	38
26	EMS characteristics	39
27	ESD characteristics	40
28	I/O static characteristics	40
29	Output voltage characteristics	41
30	I/O AC characteristics ⁽¹⁾	
31	NRST pin characteristics	
32	TIMx ⁽¹⁾ characteristics	44
33	I2C characteristics	
34	SPI characteristics ⁽¹⁾	46
35	ADC characteristics	
36	Maximum R_{AIN} at f_{ADC} = 15MHz ⁽¹⁾	
37	ADC Accuracy - Limit Test Conditions $^{(1)(2)}$	52
38	Temperature sensor characteristics $^{(3)}$	
39	Comparator characteristics	
40	LQFP48 mechanical data	57
41	LQFP32 mechanical data	58
42	QFN32 mechanical data	60

43	QFN20 mechanical data	62
44	TSSOP20 mechanical data	64
45	Document revision history	67

Introduction

Introduction

1.1 Description

MM32SPIN05x(named as "the device" throughout this document) is ARM® CortexTM-M0 32-bit RISC core based micro controller family. The device has high speed embedded memory and the CPU, memory and AHB bus subsystem speed can attain up to 72MHz. The device also has integrated with extensive range of enhanced I/Os, two APB buses peripherals, 1 12-bit ADC, 1 Comparator, 1 general purpose 16-bit timer, 1 general purpose 32-bit timer, 3 Basic timers, 1 Advanced 16-bit timer, and standard communication interfaces device: 1 I2C, 2 SPIs, and 2 UARTs.

The device works between 2.0V to 5.5V range. The normal temperature for the device is -40°C to +85°C and -40°C to +105°C extended temperature range devices are also available upon ordering. A comprehensive set of power-saving mode allows the design of low-power applications.

The devices are available in 5 different packages: LQFP48, LQFP32, QFN32, QFN20 and TSSOP20. Depending on the device chosen, different sets of peripherals are included.

The abundant peripheral configurations enable the device to fit wide range of applications in difference industries, Few examples are as follows:

- Motor drive and application control
- · Healthcare and fitness equipment
- · PC peripherals, gaming, GPS equipment
- Industrial Applications: Programmable Controllers (PLCs), Inverters, Printers and Scanners
- · Alarm system, wired and wireless sensors, video intercom

1.2 Product Features

- · Core and system
 - ARM® CortexTM-M0 CPU
 - Maximum operating frequency is up to 72MHz
 - Single cycle 32-bit hardware multiplier
 - Hardware divider(32bit)
- · Memories
 - 32K Bytes of Flash memory

- 4K Bytes of SRAM
- Boot loader support Chip Flash and ISP (In-System Programming)
- · Clock, reset and power management
 - 2.0V to 5.5V application supply
 - Power-on/Power-down reset (POR/PDR), Programmable voltage detector (PVD)
 - External 2 to 24MHz high speed crystal oscillator
 - Embedded factory-tuned 48/72MHz high speed oscillator
 - Embedded 40KHz low speed oscillator
- · Low-power
 - Sleep, Stop and Standby modes
- 1 12-bit ADC, 1µS A/D converters (up to 13 channels)
 - Conversion range: 0 to V_{DDA}
 - Support sampling time and resolution configuration
 - On-chip temperature sensor
 - On-chip voltage sensor
- 1 Comparator
- · 5 DMA controller
 - Supported peripherals: Timer, UART, I2C, SPI and ADC
- Up to 39 fast I/Os:
 - All mappable on 16 external interrupt vectors
 - Almost all can work on 5V
- · Debug mode
 - Serial wire debug (SWD)
- Up to 9 timers
 - 1 16-bit 4-channel advanced-control timer for 4 channels PWM output, with deadtime generation and emergency stop
 - 1 16-bit timer and 1 32-bit timer, with up to 4 IC/OC, usable for IR control decoding
 - 2 16-bit timer, with 1 IC/OC, 1 OCN, deadtime generation and emergency stop and modulator gate for IR control
 - 1 16-bit timer, with 1 IC/OC
 - 2 watchdog timers (independent and window type)
 - SysTick timer: 24-bit downcounter
- · Up to 5 Communication interfaces
 - 2 UARTs
 - 1 I2C
 - 2 SPIs
- 96-bit unique ID (UID)
- Packages LQFP48, LQFP32, QFN32, QFN20 and TSSOP20

For more information about the complete product, refer to Section 2.2 of the data sheet. The relevant information about the CortexTM-M0, please refer to CortexTM-M0 technical reference manual.

Specification

Specification

2.1 Device contrast

Table 1. MM32SPIN05x device features and peripheral counts

	Device	MM32SPIN05PF	MM32SPIN05PT	MM32SPIN05NT	MM32SPIN05NW/TV					
Peripheral		WIWI325PINU3PF	WIWI325PINU5PI	MINI323PINU3N I	WIWI323FIINUSINW/IW					
Flash r	nemory -K Bytes	32	32	32	32					
SR	AM -K Bytes	4	4	4	4					
Timers	General purpose (16 bit)	4	4	4	4					
	General purpose (32 bit)	1	1	1	1					
	Advanced control	1	1	1	1					
Common	UART	2	2	2	2					
	I2C	1	1	1	1					
interfaces	SPI	2	1	1	1					
	GPIOs	39	25	27	16					
	12-bit ADC per of channels)	1 13 channels								
С	omparators	1								
Max	CPU frequency		72 MHz							
Оре	rating voltage		2.0V	~ 5.5V						
	Packages	LQFP48	LQFP32	QFN32	QFN20/TSSOP20					

2.2 Summary

2.2.1 ARM® CortexTM-M0 and SRAM

The ARM® CortexTM-M0 is a generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding

computational performance and an advanced system response to interrupts.

The ARM® CortexTM-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The devices have embedded ARM core and are compatible with all ARM tools and software.

2.2.2 Memory

32K Bytes of embedded Flash memory.

2.2.3 SRAM

4K Bytes of embedded SRAM.

2.2.4 Clocks and startup

When the system is powered up, the default clock is from PLL with the resource from HSE 48 MHz oscillator. An external 2 \sim 24 MHz clock can also be configured to monitor the system during power up phases.

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 72MHzz.Refer to figure 2 for the clock drive block diagram.

2.2.5 Nested vectored interrupt controller (NVIC)

The device embeds a nested vectored interrupt controller and is able to handle up to 68 maskable interrupt channels (not including the 16 interrupt lines of Cortex[™]-M0) with 16 priority levels.

- · Closely coupled NVIC gives low latency interrupt processing
- · Interrupt entry vector table address passed directly to the core
- · Closely coupled NVIC core interface
- · Allows early processing of interrupts
- · Processing of late arriving higher priority interrupts
- · Support for tail-chaining
- · Processor state automatically saved
- · Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.2.6 Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of many edge detector lines are used to generate interrupt/event requests for waking up the system. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the internal APB2 clock period. All GPIOs can be connected to the 16 external interrupt lines.

2.2.7 Boot modes

At startup, the boot pin and boot selector option bit are used to select one of the three boot options:

- · Boot from User Flash memory
- · Boot from System Memory
- · Boot from embedded SRAM

2.2.8 Power supply schemes

- V_{DD} = 2.0V ~ 5.5V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , V_{DDA} = 2.0V \sim 5.5V: Provides power to the reset module and oscillator. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} .

2.2.9 Power supply supervisors

The device has integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 1.8V. The device remains in reset mode when the monitored supply voltage is below a specified threshold $V_{POR/PDR}$, without the need for an external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when VDD drops below the V_{PVD} threshold and/or when VDD is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

2.2.10 Voltage regulator

The voltage regulator converts the external voltage to the internal digital logic and it is always enabled after reset.

2.2.11 Low-power modes

The device support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources.

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

Stop mode achieves very low power consumption while retaining the content of SRAM and registers. the HSI and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

Standby mode

Standby mode achieves the lowest power consumption of the system. This mode turns off the voltage regulator in CPU deep sleep mode. The entire 1.5V power supply area is powered down. HSI and HSE oscillators are also powered down. SRAM and register contents are missing.

2.2.12 Direct memory access controller (DMA)

The 5-channel general-purpose DMAs manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA supports circular buffer management, removing the need for user code intervention when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

DMA can be used with the main peripherals: UART、I2C、SPI、ADC general-purpose and advanced-control timers TIMx.

2.2.13 Timers and watchdogs

Medium capacity device include 1 advanced control 2 general-purpose timers 3 base-timer 2 watchdog timers and 1 SysTick timer.

The following table compares the features of the different timers:

Table 2. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/- compare channels	Complem -entary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	Yes

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/- compare channels	Complem -entary outputs
General	TIM2	32-bit	Up, down, up/down	integer from 1 to $2^{32} - 1$	Yes	4	No
purpose	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	No
basic	TIM14	16-bit	Up	integer from 1 to 65536	Yes	1	No
Dasic	TIM16 / TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	Yes

Advanced-control timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM multiplexed on six channels. It has complementary PWM outputs with programmable inserted dead times. It can also be seen as a complete general-purpose timer. The four independent channels can be used for:

- · Input capture
- · Output compare
- PWM generation (edge or center-aligned modes)
- One-pulse mode output

If configured as a standard 16-bit timer, it has the same features as the TIMx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0 \sim 100%).

In debug mode, the counter can be frozen and the PWM output is disabled to cut off the switches controlled by these outputs.

Many features are shared with those of the standard timers which have the same architecture. The advanced control timer can therefore work together with the other timers via the Timer Link feature for synchronization or event chaining.

General-purpose timers (TIMx)

There are 2 synchronizable general-purpose timers (TIM2 TIM3).

General-purpose timers 32-bit

The timer is based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The feature is 4 independent channels each for input capture/output compare, PWM or one-

pulse mode output.

General-purpose timers 16-bit

TIM₃

The timer is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. The feature is 4 independent channels each for input capture/output compare, PWM or one-pulse mode output.

The timer can work together or with the TIM1 advanced-control timer via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs. They all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Basic timer

TIM14

This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM14 features one single channel for input capture/output compare, PWM or one-pulse mode output. Their counter can be frozen in debug mode.

TIM16/TIM17

Every timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. They each have a single channel for input capture/output compare, PWM or one-pulse mode output. TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation. Their counters can be frozen in debug mode.

Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 KHz internal oscillator and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- · A 24-bit down counter
- · Autoreload capability
- · Maskable system interrupt generation when the counter reaches 0
- · Programmable clock source

2.2.14 Universal asynchronous receiver/transmitter (UART)

UART provides hardware management of the CTS, RTS.

Support LIN master-slave function.

All UART interface can be served by the DMA controller.

2.2.15 I2C interface

The I2C interface can operate in multimaster or slave modes. It can support Standard mode, and Fast Mode.

It supports 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (two addresses, one with configurable mask).

2.2.16 Serial peripheral interface (SPI)

The SPI interface, in slave or master mode, can be configured to 1 \sim 32 bits per frame.

All SPI interface can be served by the DMA controller.

2.2.17 General-purpose inputs/outputs (GPIO)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. The I/O configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

2.2.18 Analog-to-digital converter (ADC)

The one 12-bit analog-to-digital converters is embedded into microcontrollers and the ADC shares up to 10 external channels, performing conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs. The ADC can be served by the DMA controller.

The analog watchdog function allows very precise monitoring of all the way, multiple or all selected channels, and an interruption occurs when the monitored signal exceeds the preset threshold. The events generated by the general-purpose timers (TIMx) and the advanced-control timer (TIM1) can be internally connected to the ADC start trigger to allow the application to synchronize A/D conversion and timers.

2.2.19 Hardware Dvision

The hardware division unit consists of four 32-bit data registers, which are dividend, divisor, quotient and remainder, and can be done with signed or unsigned 32-bit division. The hardware division control register USIGN can choose whether to have signed division or unsigned division.

Each time the divisor register is written, the division operation is automatically triggered. After the operation is completed, the result is written to the quotient and remainder registers. If the reader register, remainder register, or status register is read before the end, the read operation is suspended until the end of the operation.

If the divisor is zero, an overflow interrupt flag will be generated.

2.2.20 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The temperature sensor is internally connected to the input channel which is used to convert the sensor output voltage into a digital value.

2.2.21 Serial single line SWD debug port (SW-DP)

Built-in ARM two-wire serial debug port (SW-DP).

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

2.2.22 Comparator (COMP)

The devices embed 1 general purpose comparators. that can be used either as standalone devices (all terminal are available on I/Os) or combined with the timers. The comparators can be used for a variety of functions including:

- · Wake-up from low-power mode triggered by an analog signal,
- · Analog signal conditioning,
- Cycle-by-cycle current control loop when combined with the PWM output from a timer.
- · Rail-to-rail comparators
- · Each comparator has positive and configurable negative inputs used for flexible voltage
- · Selection:
 - Reusable I/O pins
 - Internal comparison voltage CRV selects the voltage divider value of AVDD or internal reference voltage
- Programmable hysteresis

- Programmable speed/consumption
- The outputs can be redirected to an I/O or to timer inputs for triggering:
 - Capture events
 - OCref_clr events (for cycle-by-cycle current control)
 - Break events for fast PWM shutdowns

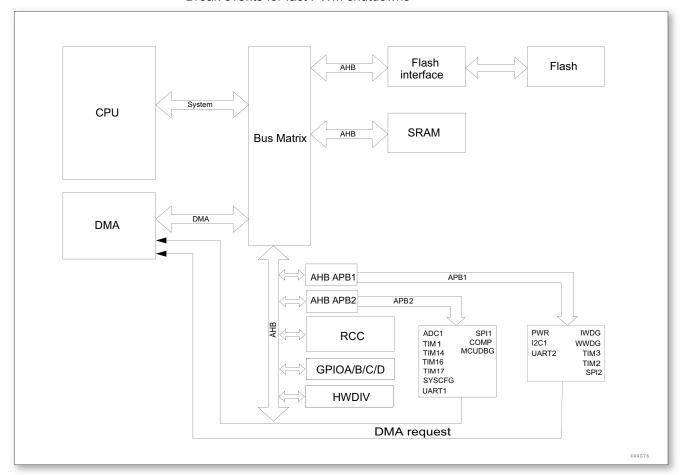


Figure 1. Block diagram

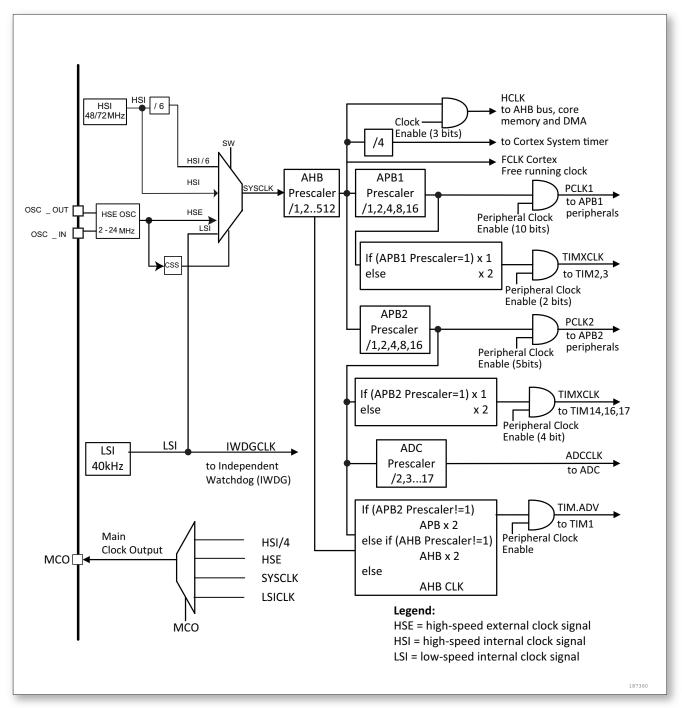


Figure 2. Clock tree

Pin definition

Pin definition

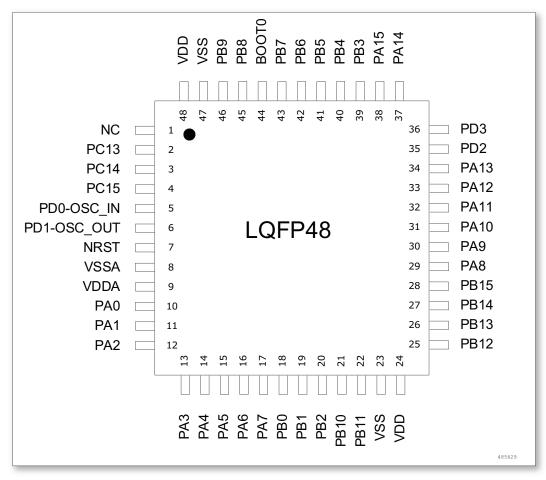


Figure 3. LQFP48 packet pinout

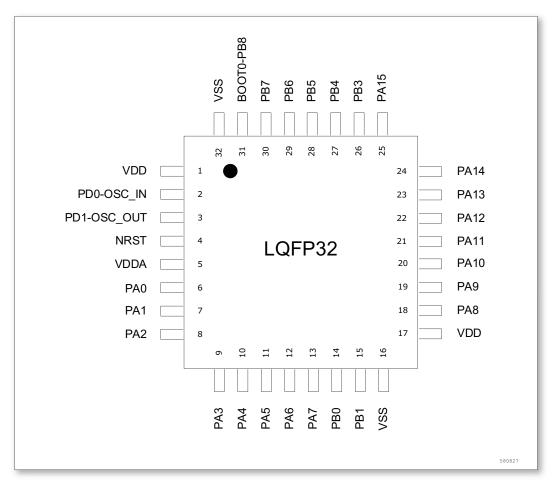


Figure 4. LQFP32 packet pinout

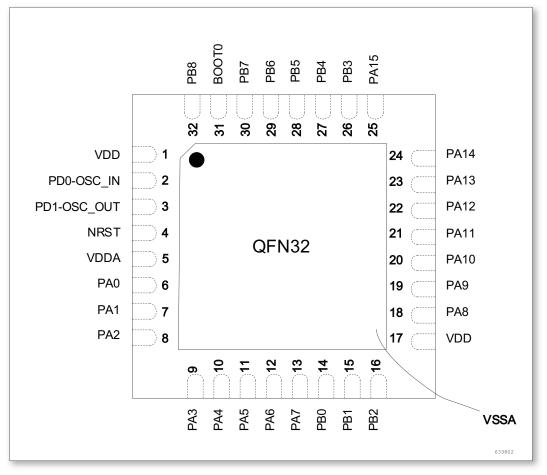


Figure 5. QFN32 packet pinout

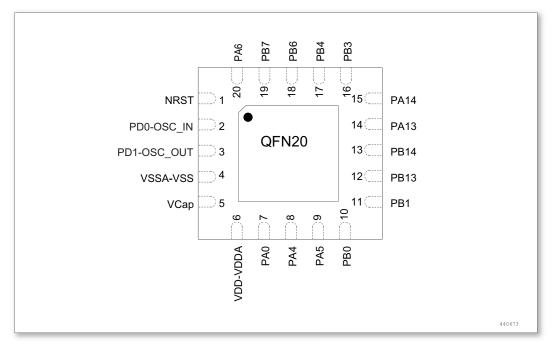


Figure 6. QFN20 packet pinout

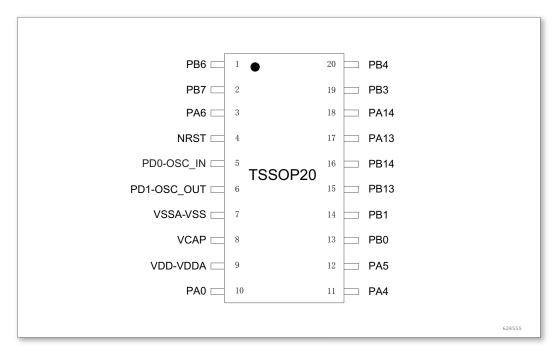


Figure 7. TSSOP20 packet pinout

annotate: VCap should be setted to float or connect to ground with 0.1uF-0.01uF capacitor.

Table 3. Pin definitions

	Pin number								Alternate	Additional
LQFP	LQFP	QFN	TSSOP	QFN	Pin name	Type ⁽¹⁾	1/0	Main function	functions	functions
48	32	32	20	20			structure ⁽²⁾		tunctions	tunctions
1	-	-	-	-	NC	S	-	NC	-	-
2	-	-	-	-	PC13	I/O	FT	PC13	TIM2_CH1	-
3	-	-	-	-	PC14	I/O	FT	PC14	TIM2_CH2	-
4	-	-	-	-	PC15	I/O	FT	PC15	TIM2_CH3	-
5	2	2	5	2	PD0 OSC_IN	I/O	FT	PD0	I2C1_SDA	-
6	3	3	6	3	PD1 OSC_OUT	I/O	FT	PD1	I2C1_SCL	-
7	4	4	4	1	NRST	I/O	FT	NRST	-	-
8	-	0	-	4	VSSA	S	-	VSSA	-	-
9	5	5	9	6	VDDA	S	-	VDDA	-	-
10	6	6	10	7	PA0	I/O	TC	PA0	UART2_CTS/ TIM2_CH1_ETR/ SPI2_NSS/	ADC1_VIN[0]
									TIM2_CH3/ COMP1_OUT	
11	7	7	-	-	PA1	I/O	тс	PA1	UART2_RTS/ TIM2_CH2	ADC1_VIN[1]/ COMP1_INP[0]

	Pin number						1/0		Altamata	A dditional																					
LQFP	LQFP	QFN	TSSOP	QFN	Pin name	Type ⁽¹⁾	I/O structure ⁽²⁾	Main function	Alternate functions	Additional functions																					
48	32	32	20	20			Structure		Tunctions	Tunctions																					
									UART2_TX/	ADC1_VIN[2]/																					
12	8	8	-	-	PA2	I/O	TC	PA2	TIM2_CH3/	COMP1_INP[1]																					
									SPI2_NSS																						
13	9	9	-	-	PA3	I/O	TC	PA3	UART2_RX/	ADC1_VIN[3]/																					
									TIM2_CH4	COMP1_INP[2]																					
									SPI1_NSS/																						
14	10	10	11	8	PA4	I/O	TC	PA4	TIM1_BKIN/	ADC1_VIN[4]/																					
									TIM14_CH1/	COMP1_INP[3]																					
									I2C1_SDA																						
									SPI1_SCK/																						
									TIM2_CH1_ETR/	ADC1_VIN[5]/																					
15	11	11 12	11 12	11	11	11 12	12	12	12	9	PA5	I/O	TC	PA5	TIM1_ETR/	COMP1_INM[0]															
							I2C1_SCL/	I2C1_SCL/	I2C1_SCL/	r.a1																					
									TIM1_CH3N																						
									SPI1_MISO/																						
									TIM3_CH1/																						
									TIM1_BKIN/																						
16	12	12	3	20	PA6	I/O	TC	PA6	UART2_RX/	ADC1_VIN[6]/																					
10	12	12		20	1710			1710	TIM1_ETR/	COMP1_INM[1]																					
									TIM16_CH1/																						
									TIM1_CH3/																						
									COMP1_OUT																						
									SPI1_MOSI/																						
									TIM3_CH2/																						
									TIM1_CH1N/	ADC1_VIN[7]/																					
17	13	13	-	-	PA7	I/O	TC	PA7	TIM14_CH1/																						
									TIM17_CH1/	COMP1_INM[2]																					
									TIM1_CH2N/																						
									TIM1_CH3N																						
									TIM3_CH3/																						
18	14	14	12	10	PB0	1/0	TC	PB0	TIM1_CH2N/	ADC4 MAIG																					
10	14	14	13	10	FDU	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	TC	TC	IC	IC	I C	FDU	TIM1_CH1N/	ADC1_VIN[8]
									TIM1_CH3																						

	Pin number						1/0		Altamata	A dditional							
LQFP	QFP LQFP QFN TS	TSSOP	QFN	Pin name	Type ⁽¹⁾	I/O structure ⁽²⁾	Main function	Alternate functions	Additional								
48	32	32	20	20			Structure	ie /	tunctions	functions							
									TIM14_CH1/								
									TIM3_CH4/								
									TIM1_CH3N/								
19	15	15	14	11	PB1	I/O	тс	PB1	TIM1_CH4/	ADC1 VINIO							
19	13	15	14	''	1 61	1/0	10	PB.I	TIM1_CH2N/	ADC1_VIN[9]							
									MCO/								
									TIM1_CH2/								
									TIM1_CH1N								
20	-	16	-	-	PB2	I/O	FT	PB2	-	-							
									I2C1_SCL/								
21	-	-	-	-	PB10	I/O	FT	PB10	TIM2_CH3/	-							
									SPI2_SCK								
22	_	_	_	_	PB11	I/O	FT	PB11	I2C1_SDA/								
		_			1 511	1/0		1 011	TIM2_CH4	_							
23	16	0	7	4	VSS	S	-	VSS	-	-							
24	17	17	9	6	VDD	S	-	VDD	-	-							
											SPI2_NSS/						
											SPI2_SCK/						
25	-	-	-	-	-	-	-	-	-	-	-	PB12	I/O	FT	PB12	TIM1_BKIN/	-
									SPI2_MOSI/								
									SPI2_MISO								
											SPI2_SCK/						
									SPI2_MISO/								
									TIM1_CH1N/								
26	_	_	15	12	PB13	I/O	FT	PB13	SPI2_NSS/								
20	_	-	13	12	1 613	1/0	''	1 013	SPI2_MOSI/	-							
									I2C1_SCL/								
									TIM1_CH3N/								
									TIM2_CH1								
									SPI2_MISO/								
									SPI2_MOSI/								
									TIM1_CH2N/								
27			16	12	DD1 <i>1</i>	I/O	FT	PB14	SPI2_SCK/								
21	_	-	16 13	13	PB14	1/0	ΓI 	FD1 4	SPI2_NSS/	-							
									I2C1_SDA/								
									TIM1_CH3/								
									TIM1_CH1								

	Pir	numk	er				1/0		Altamata Additional																																								
LQFP	LQFP	QFN	TSSOP	QFN	Pin name	Type ⁽¹⁾	I/O structure ⁽²⁾	Main function	Alternate functions	Additional																																							
48	32	32	20	20			structure		tunctions	functions																																							
									SPI2_MOSI/																																								
									SPI2_NSS/																																								
						I/O	FT		TIM1_CH3N/																																								
28	-	-	-	-	PB15			PB15	SPI2_MISO/	-																																							
									SPI2_SCK/																																								
										TIM1_CH2N/																																							
									TIM1_CH2																																								
									MCO/																																								
29	18	18	_	_	PA8	I/O	FT	PA8	TIM1_CH1/	_																																							
20	10	10			1710	""		17.0	TIM1_CH2/	_																																							
													TIM1_CH3																																				
									UART1_TX/																																								
									TIM1_CH2/																																								
	19								UART1_RX/																																								
30		19	19	19	-	-	PA9	I/O	FT	PA9	I2C1_SCL/	-																																					
										MCO/																																							
									TIM1_CH1N/																																								
									TIM1_CH4																																								
																																																TIM17_BKIN/	
									UART1_RX/																																								
		20		-						TIM1_CH3/																																							
31	20		20 -		-	-	-	-	-	-	-	PA10	I/O	FT	PA10	UART1_TX/	-																																
														I2C1_SDA/																																			
									TIM1_CH1/																																								
									SPI2_SCK																																								
									UART1_CTS/																																								
									TIM1_CH4/																																								
32	21	21	-	-	PA11	I/O	FT	PA11	SPI2_MOSI/	-																																							
									I2C1_SCL/																																								
									COMP1_OUT																																								
									UART1_RTS/																																								
		22 22 PA12					TIM1_ETR/																																										
33	22		22 22	22 22 -	22 -	22	-	PA12	I/O	FT	PA12	SPI2_MISO/	-																																				
										I2C1_SDA/																																							
									TIM1_CH2																																								

	Pir	numb	per				1/0		Altamata	A dditional
LQFP	LQFP	QFN	TSSOP	QFN	Pin name	Type ⁽¹⁾	I/O structure ⁽²⁾	Main function	Alternate functions	Additional functions
48	32	32	20	20			Structure		lulicuolis	Tunctions
									SWDIO/	
									SPI2_MISO/	
34	23	23	17	14	PA13	I/O	FT	PA13	MCO/	-
									TIM1_CH2/	
									TIM1_BKIN	
35	-	-	-	-	PD2	I/O	FT	PD2	-	-
36	-	-	-	-	PD3	I/O	FT	PD3	-	-
									SWDCLK/	
37	24	24	18	15	PA14	I/O	FT	PA14	UART2_TX/	-
									SPI1_NSS	
									SPI1_NSS/	
38	25	25	-	-	PA15	I/O	FT	PA15	UART2_RX/	-
									TIM2_CH1_ETR	
									SPI1_SCK/	
									TIM2_CH2/	
39	26	26	19	16	PB3	3 I/O TC PB3 UART1_TX/	ADC1_VIN[10]			
39	20	20	19	10	1 03	"0	10	1 55	TIM2_CH3/	ADC1_VIN[10]
									TIM1_CH1/	
									TIM2_CH1	
									SPI1_MISO/	
									TIM3_CH1/	
40	27	27	20	17	PB4	I/O	TC	PB4	UART1_RX/	ADC1_VIN[11]
40	21	21	20	''	1 04	1/0	10	1 64	TIM17_BKIN/	ADC1_VIIV[11]
									TIM1_CH2/	
									TIM2_CH2	
									SPI1_MOSI/	
									TIM3_CH2/	
41	28	28	_	_	PB5	I/O	FT	PB5	TIM16_BKIN/	
71	20	20	-	-	1 03	"0	''	1 65	MCO/	-
									TIM1_CH3/	
									TIM2_CH3	
									UART1_TX/	
42	29	29	1	18	PB6	I/O	FT	PB6	I2C1_SCL/	
44	23	23	'	10	1.00	"0	F1	FDU	TIM16_CH1N/	-
									TIM2_CH1	

	Pir	numk	er				I/O		Alternate	Additional	
LQFP	LQFP	QFN	TSSOP	QFN	Pin name	Type ⁽¹⁾	structure ⁽²⁾	Main function	functions	functions	
48	32	32	20	20			Structure		lunctions	lunctions	
									UART1_RX/		
43	30	30	2	19	PB7	I/O	тс	PB7	I2C1_SDA/	ADC1_VIN[12]	
43	30	30	2	19	FD/	1/0	10	PB/	TIM17_CH1N/	ADC1_VIN[12]	
									UART2_TX		
44	31	31	-	-	воото	ı	FT	воото	-	-	
									I2C1_SCL/		
45	31	32	-	-	PB8	I/O	FT	PB8	TIM16_CH1/	-	
									UART2_RX		
									I2C1_SDA/		
46		_		_	PB9	I/O	FT	PB9	TIM17_CH1/		
40	-	-	-	-	ГБЭ	1/0	FI	F F F F F F F F F F F F F F F F F F F	TIM1_CH4/	-	
									SPI2_NSS		
47	32	0	-	4	VSS	S	-	VSS	-	-	
48	1	1	-	6	VDD	S	-	VDD	-	-	
				5	VCap	S		1.5V regulator			
	-	-	-	5	v Cap	٥	_	capacitor	-	_	

- 1. I = input, O = output, S = power supply, HiZ = high resistance.
- 2. FT: 5V tolerant, Input signal should be between VDD and 5V. TC: Standard I/O, Input signal does not exceed VDD.

Table 4. Alternate functions for port A

Pin	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	
Name	AFU	AFI	AFZ	AFJ	AF4	AFS	AFO		
- DAG		LIADTO OTO	TIM2_CH1	ODIO NOO	TIMO OLIO			COMP4 OUT	
PA0	-	UART2_CTS	_ETR	SPI2_NSS	TIM2_CH3	-	-	COMP1_OUT	
PA1	-	UART2_RTS	TIM2_CH2	-	-	-	-	-	
PA2	-	UART2_TX	TIM2_CH3	SPI2_NSS	-	-	-	-	
PA3	-	UART2_RX	TIM2_CH4	-	-	-	-	-	
PA4	SPI1_NSS	-	-	TIM1_BKIN	TIM14_CH1	I2C1_SDA	-	-	
PA5	SDI4 SCK		TIM2_CH1	TIM4 ETD		I2C1 SCL	TIM1 CUSNI		
FAS	SPI1_SCK	-	_ETR	TIM1_ETR	-	1201_30L	TIM1_CH3N	-	
PA6	SPI1_MISO	TIM3_CH1	TIM1_BKIN	UART2_RX	TIM1_ETR	TIM16_CH1	TIM1_CH3	COMP1_OUT	
PA7	SPI1_MOSI	TIM3_CH2	TIM1_CH1N	-	TIM14_CH1	TIM17_CH1	TIM1_CH2N	TIM1_CH3N	
PA8	MCO	-	TIM1_CH1	-	-	-	TIM1_CH2	TIM1_CH3	
PA9	-	UART1_TX	TIM1_CH2	UART1_RX	I2C1_SCL	MCO	TIM1_CH1N	TIM1_CH4	
PA10	TIM17_BKIN	UART1_RX	TIM1_CH3	UART1_TX	I2C1_SDA	-	TIM1_CH1	SPI2_SCK	
PA11	-	UART1_CTS	TIM1_CH4	-	SPI2_MOSI	I2C1_SCL	-	COMP1_OUT	

Pin	A.F.O.	A F.4	A.F.O.	A.F.2	AF4	AFF	AFC	A F.7	
Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	
PA12	-	UART1_RTS	TIM1_ETR	-	SPI2_MISO	I2C1_SDA	-	TIM1_CH2	
PA13	SWDIO	-	-	-	SPI2_MISO	MCO	TIM1_CH2	TIM1_BKIN	
PA14	SWDCLK	UART2_TX	-	SPI1_NSS	-	-	-	-	
PA15	SPI1_NSS	UART2_RX	TIM2_CH1 _ETR	-	-	-	-	-	

Table 5. Alternate functions for port B

Pin	450	A F.4	A.F.O.	AFO	A F 4	A F 5	AFC	A F.7
Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PB0	-	TIM3_CH3	TIM1_CH2N	TIM1_CH1N	TIM1_CH3	-	-	-
PB1	TIM14_CH1	TIM3_CH4	TIM1_CH3N	TIM1_CH4	TIM1_CH2N	MCO	TIM1_CH2	TIM1_CH1N
PB3	SPI1_SCK	-	TIM2_CH2	UART1_TX	TIM2_CH3	-	TIM1_CH1	TIM2_CH1
PB4	SPI1_MISO	TIM3_CH1	-	UART1_RX	-	TIM17_BKIN	TIM1_CH2	TIM2_CH2
PB5	SPI1_MOSI	TIM3_CH2	TIM16_BKIN	MCO	-	-	TIM1_CH3	TIM2_CH3
PB6	UART1_TX	I2C1_SCL	TIM16_CH1N	-	TIM2_CH1	-	-	-
PB7	UART1_RX	I2C1_SDA	TIM17_CH1N	-	UART2_TX	-	-	-
PB8	-	I2C1_SCL	TIM16_CH1	-	UART2_RX	-	-	-
PB9	-	I2C1_SDA	TIM17_CH1	-	TIM1_CH4	SPI2_NSS	-	-
PB10	-	I2C1_SCL	TIM2_CH3	-	-	SPI2_SCK	-	-
PB11	-	I2C1_SDA	TIM2_CH4	-	-	-	-	-
PB12	SPI2_NSS	SPI2_SCK	TIM1_BKIN	SPI2_MOSI	SPI2_MISO	-	-	-
PB13	SPI2_SCK	SPI2_MISO	TIM1_CH1N	SPI2_NSS	SPI2_MOSI	I2C1_SCL	TIM1_CH3N	TIM2_CH1
PB14	SPI2_MISO	SPI2_MOSI	TIM1_CH2N	SPI2_SCK	SPI2_NSS	I2C1_SDA	TIM1_CH3	TIM1_CH1
PB15	SPI2_MOSI	SPI2_NSS	TIM1_CH3N	SPI2_MISO	SPI2_SCK	-	TIM1_CH2N	TIM1_CH2

Table 6. Alternate functions for port C

Pin	AF0	AF1	A E 2	AF3	AF4	AF5	AEG	A = 7
Name		AFT	AF2	AFS	AF4	AF5	AF6	AF7
PC13	-	-	-	-	-	-	TIM2_CH1	-
PC14	-	-	-	-	-	-	TIM2_CH2	-
PC15	-	-	-	-	-	-	TIM2_CH3	-

Table 7. Alternate functions for port D

Pin	AF0	A E 4	AE2	AE2	A E 4	AF5	AFG	A = 7
Name		AF1	AF2	AF3	AF4	AFS	AF6	AF7
PD0	-	I2C1_SDA	-	-	-	-	-	-
PD1	-	I2C1_SCL	-	-	-	-	-	-

Memory mapping

Memory mapping

Table 8. Memory mapping

Bus	Boundaryaddress	Size	Peripheral	Notes
			Main flash memory, system	
	0x0000 0000 - 0x0001 FFFF	128 KB	memory, or SRAM, depends on	
			the configuration of BOOT	
	0x0002 0000 - 0x07FF FFFF	~ 128 MB	Reserved	
	0x0800 0000 - 0x0800 7FFF	32 KB	Main Flash memory	
	0x0800 8000 - 0x1FFD FFFF	~ 256 MB	Reserved	
Flash	0x1FFE 0000 - 0x1FFE 01FF	0.5 KB	Reserved	
	0x1FFE 0200 - 0x1FFE 0FFF	3 KB	Reserved	
	0x1FFE 1000 - 0x1FFE 1BFF	3 KB	Reserved	
	0x1FFE 1C00 - 0x1FFF F3FF	~ 256 MB	Reserved	
	0x1FFF F400 - 0x1FFF F7FF	1 KB	System memory	
	0x1FFF F800 - 0x1FFF F80F	16 B	Option bytes	
	0x1FFF F810 - 0x1FFF FFFF	~ 2 KB	Reserved	
CDAM	0x2000 0000 - 0x2000 0FFF	4 KB	SRAM	
SRAM -	0x2000 1000 - 0x2FFF FFFF	~ 512 MB	Reserved	
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2	
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3	
	0x4000 0800 - 0x4000 27FF	8 KB	Reserved	
	0x4000 2800 - 0x4000 2BFF	1 KB	Reserved	
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG	
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG	
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved	
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2	
APB1	0x4000 4000 - 0x4000 43FF	1 KB	Reserved	
	0x4000 4400 - 0x4000 47FF	1 KB	UART2	
	0x4000 4800 - 0x4000 4BFF	3 KB	Reserved	
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1	
	0x4000 5800 - 0x4000 5BFF	1 KB	Reserved	
	0x4000 5C00 - 0x4000 5FFF	1 KB	Reserved	
	0x4000 6000 - 0x4000 63FF	1 KB	Reserved	
	0x4000 6400 - 0x4000 67FF	1 KB	Reserved	
	0x4000 6800 - 0x4000 6BFF	1 KB	Reserved	

Bus	Boundaryaddress	Size	Peripheral	Notes
	0x4000 6C00 - 0x4000 6FFF	1 KB	Reserved	
APB1	0x4000 7000 - 0x4000 73FF	1 KB	PWR	
	0x4000 7400 - 0x4000 FFFF	35 KB	Reserved	
	0x4001 0000 - 0x4001 03FF	1 KB	SYSCFG	
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI	
	0x4001 0800 - 0x4001 23FF	7 KB	Reserved	
	0x4001 2400 - 0x4001 27FF	1 KB	ADC1	
	0x4001 2800 - 0x4001 2BFF	1 KB	Reserved	
	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1	
APB2	0x4001 3000 - 0x4001 33FF	1 KB	SPI1	
	0x4001 3400 - 0x4001 37FF	1 KB	DBGMCU	
	0x4001 3800 - 0x4001 3BFF	1 KB	Reserved	
	0x4001 3C00 - 0x4001 3FFF	1 KB	COMP	
	0x4001 4000 - 0x4001 43FF	1 KB	TIM14	
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16	
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17	
	0x4001 4C00 - 0x4001 7FFF	13 KB	Reserved	
	0x4002 0000 - 0x4002 03FF	1 KB	DMA	
	0x4002 0400 - 0x4002 0FFF	3 KB	Reserved	
	0x4002 1000 - 0x4002 13FF	1 KB	RCC	
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved	
	0x4002 2000 - 0x4002 23FF	1 KB	Flash interface	
	0x4002 2400 - 0x4002 5FFF	15 KB	Reserved	
AHB	0x4002 6000 - 0x4002 63FF	1 KB	Reserved	
	0x4002 6400 - 0x4002 FFFF	39 KB	Reserved	
	0x4003 0000 - 0x4003 03FF	1 KB	HDIV	
	0x4003 0400 - 0x47FF FFFF	~ 128 MB	Reserved	
	0x4800 0000 - 0x4800 03FF	1 KB	GPIOA	
	0x4800 0400 - 0x4800 07FF	1 KB	GPIOB	
	0x4800 0800 - 0x4800 0BFF	1 KB	GPIOC	
	0x4800 0C00 - 0x4800 0FFF	1 KB	GPIOD	
	0x4800 1000 - 0x5FFF FFFF	~ 384 MB	Reserved	

Electrical characteristics

Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed with an ambient temperature at $T_A = 25$ °C, $V_{DD} = 3.3$ V.

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25^{\circ}C$ and $V_{DD} = 3.3V$. They are given only as design guidelines and are not tested.

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The load conditions used for pin parameter measurement are shown in the figure below.

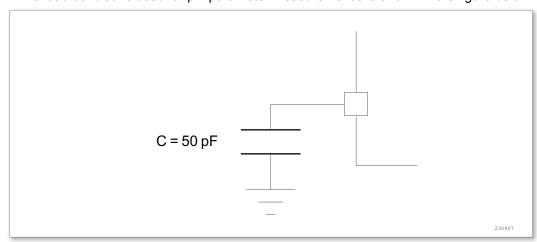


Figure 8. Pin loading conditions

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is shown in the figure below.

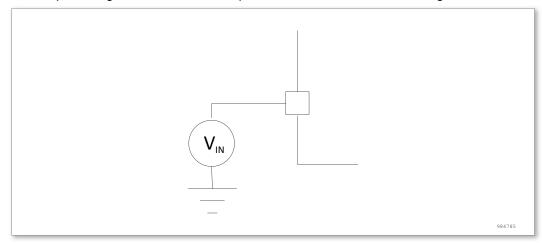


Figure 9. Pin input voltage

5.1.6 Power supply scheme

The power supply design scheme is shown in the figure below.

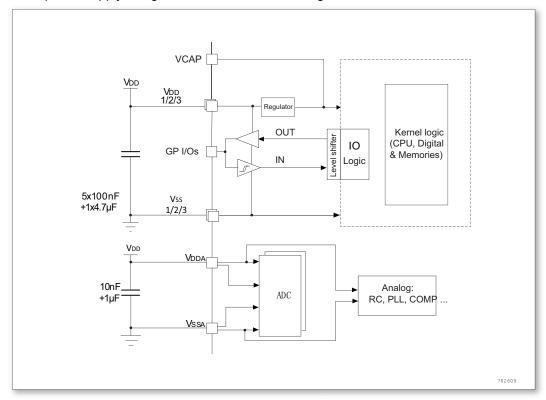


Figure 10. Power supply scheme

5.1.7 Current consumption measurement

The measurement of the current consumption on the pin is shown in the figure below.

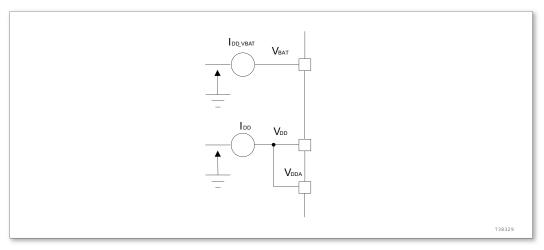


Figure 11. Current consumption measurement scheme

5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in Tables (Table 9, Table 10, Table 11) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 9. Voltage characteristics

Symbol	Definition	Min	Max	Unit	
V _{DD} - V _{SS}	External main supply	- 0.3	5.5		
V _{DD} - V _{SS}	voltage(including V_{DDA} and $V_{\text{SSA}})^{(1)}$	- 0.3	5.5	V	
\/	Input voltage on FT and FTf pins ⁽²⁾	V _{SS} - 0.3	5.5	v	
V_{IN}	Input voltage on other $pins^{(2)}$	V _{SS} - 0.3	5.5		
	Variations between different V _{DD}		50		
$ \vartriangle V_{DDx} $	power pins		50	mV	
177 77 1	Variations between all the different	50		IIIV	
$ V_{\rm SSx} - V_{\rm SS} $	ground pins		50		

- 1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- 2. V_{IN} maximum must always be respected. Refer to Table below for maximum allowed injected current values.

Table 10. Current characteristics

Symbol	Definition	Max	Unit
I _{VDD}	Total current into sum of all V_{DD}/V_{DDA} power lines(source) ⁽¹⁾	120	mA
I _{vss}	Total current out of sum of all V _{SS} ground lines(sink) ⁽¹⁾	120	mA

Symbol	Definition	Max	Unit
I _{IO}	Output current sunk by any I/O and control pin	20	mA
I _{IO}	Output current source by any I/O and control pin	-18	mA
I _{INJ(PIN)} (2)(3)	Injected current on NRST pins	±5	mA
I _{INJ(PIN)} (2)(3)	Injected current on OSC_IN pin of HSE and OSC_IN pin of LSE	±5	mA
I _{INJ(PIN)} (2)(3)	Injected current on other pins ⁽⁴⁾	±5	mA
$\sum I_{\text{INJ(PIN)}}^{(2)}$	Total injected current(sum of all I/O and control pins) ⁽⁵⁾	±25	mA

- 1. All main power(V_{DD}, V_{DDA}) and ground(V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- 2. This current consumption must be properly distributed to all I/O and control pins. The total output current must not be poured/pulled between the two consecutive power supply pins of the reference high pin count LQFP package.
- 3. Negative injection disturbs the analog performance of the device.
- 4. When $V_{IN} > V_{DD}$, there is a forward injection current; when $V_{IN} < V_{SS}$, there is a reverse injection current.Do not exceed $I_{INJ(PIN)}$.
- 5. When several inputs are submitted to a current injection, the maximum $I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 11. Thermal characteristics

Symbol	Definition	Max	Unit	
T _{STG}	Storage temperature range	- 45 ~ + 150	°C	
т.	Maximum junction	125	°C	
IJ	temperature	125		

5.3 Operating conditions

5.3.1 General operating conditions

Table 12. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock		0	72	MHz
'HCLK	frequency		U	12	IVII IZ
£	Internal APB1 clock		0	£	MHz
f _{PCLK1}	frequency		0	f _{HCLK}	IVII⊤Z
•	Internal APB2 clock		0	£	MHz
f _{PCLK2}	frequency		0	f _{HCLK}	
V _{DD}	Standard operating		2.0	F. F.	
	voltage		2.0	5.5	V

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DDA} ⁽¹⁾	Analog operating voltage (ADC not used)	Must be the same voltage as $V_{ extsf{DD}}$	2.0	5.5	V	
	Analog operating voltage (ADC used)	Mast be the same voltage as v _{DD}	2.5	5.5		
	Ambient temperature:	Maximum power dissipation	-25	85	°C	
T _A	T _A =85°C ⁽²⁾	Low power dissipation ⁽³⁾	-25	105	°C	

- 1. It is recommended to use the same power supply for V_{DD} and V_{DDA} , the maximum permissible difference between V_{DD} and V_{DDA} is 300mVduring power up and normal operation.
- 2. If T_A is low, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (See subsec 5.1).
- 3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (See subsec 5.1).

5.3.2 Operating conditions at power-up/power-down

The parameters given in the table below are based on tests under normal operating conditions.

Table 13. Operating conditions at power-up/power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD}	V _{VDD} rise time rate	T _A = 27°C	300	∞	uS/V
	V _{VDD} fall time rate	1 _A - 27 C	300	∞	μ5/ν

5.3.3 Embedded reset and power control block characteristics

The parameters given in the table below are based on the ambient temperature and the V_{DD} supply voltage listed in Table 12.

Table 14. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{PVD}	Level selection of programmable voltage detectors	PLS[3: 0]=0000 (Rising edge)		1.82		V
		PLS[3: 0]=0000 (Falling edge)		1.71		V
		PLS[3: 0]=0001 (Rising edge)		2.12		V
		PLS[3: 0]=0001 (Falling edge)		2.00		V
		PLS[3: 0]=0010 (Rising edge)		2.41		V
		PLS[3: 0]=0010 (Falling edge)		2.30		V
		PLS[3: 0]=0011 (Rising edge)		2.71		V
		PLS[3: 0]=0011 (Falling edge)		2.60		V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		PLS[3: 0]=0100 (Rising edge)		3.01		V
		PLS[3: 0]=0100 (Falling edge)		2.90		V
		PLS[3: 0]=0101 (Rising edge)		3.31		V
		PLS[3: 0]=0101 (Falling edge)		3.19		V
		PLS[3: 0]=0110 (Rising edge)		3.61		V
		PLS[3: 0]=0110 (Falling edge)		3.49		V
	Level selection of programmable voltage detectors	PLS[3: 0]=0111 (Rising edge)		3.91		V
V_{PVD}		PLS[3: 0]=0111 (Falling edge)		3.79		V
		PLS[3: 0]=1000 (Rising edge)		4.21		V
		PLS[3: 0]=1000 (Falling edge)		4.09		V
		PLS[3: 0]=1001 (Rising edge)		4.51		V
		PLS[3: 0]=1001 (Falling edge)		4.39		V
		PLS[3: 0]=1010 (Rising edge)		4.81		V
		PLS[3: 0]=1010 (Falling edge)		4.69		V
V _{PVDhyst} ⁽²⁾	PVD hysteresis			110		mV
V _{POR/PDR}	Power on/down	Falling edge	1.63 ⁽¹⁾	1.66	1.68	V
	reset threshold	Rising edge		1.75		V
V _{PDRhys} ⁽²⁾	PDR hysteresis			90.9		mV
RSTTEMPO ⁽²⁾	Reset duration			0.61		ms

- 1. The product behavior is guaranteed by design down to the minimum value V_{POR/PDR}.
- 2. Guaranteed by design, not tested in production.

Note: The reset duration is measured from power-on (POR reset) to the time when the user application code reads the first instruction.

5.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

All Run-mode current consumption measurements given in this section are performed with a reduced code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode, and are connected to a static level V_{DD} or V_{SS} (no load)
- · All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} (0 ~ 24 MHz is 0 waiting period , 24 ~ 48 MHz is 1 waiting period, 48 ~ 72 MHz is 2 waiting period).

The instruction prefetching function is on. When the peripherals are enabled:
 f_{PCLK1} = f_{HCLK}.

Note: The instruction prefetching function must be set before setting the clock and bus divider.

Table 15. Typical and maximum current consumption in stop and standby modes⁽²⁾

Symbol	Parameter	Conditions	Max ⁽¹⁾ T _A =25°C	Unit
	Supply current in Stop mode	Enter the stop mode after reset	6	
I_{DD}	Supply current in Standby mode	Enter the standby mode after reset	0.4	μΑ

- 1. Maximum values are tested at $T_A = 25^{\circ}C$.
- 2. Data based on characterization results, not tested in production. The IO state is an analog input.

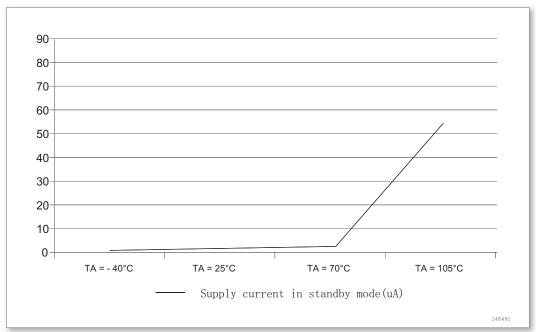


Figure 12. Typical current consumption in standby mode vs. temperature at V_{DD} = 3.3V

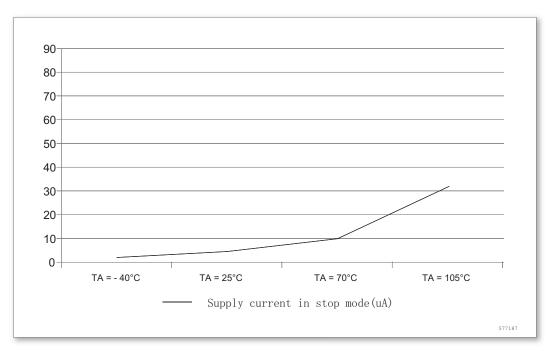


Figure 13. Typical current consumption in stop mode vs. temperature at V_{DD} = 3.3V

Typical current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input configuration, and are connected to a static level V_{DD} or V_{SS} (no load).
- · All the peripherals are closed, unless otherwise specified.
- The Flash memory access time is adjusted to the f_{HCLK} (0 \sim 24 MHz is 0 waiting period , 24 \sim 48 MHz is 1 waiting period , 48 \sim 72 MHz is 2 waiting period).
- The ambient temperature and V_{DD} supply voltage conditions are summarized in Table 12.
- The instruction prefetching function is on. When the peripherals are enabled:
 f_{PCLK1} = f_{HCLK}.

Note: The instruction prefetch function must be set before the clock is set and the bus is divided.

Table 16. Typical current consumption in Run mode, code executing from Flash

		Conditions	f _{HCLK}	Тур		
Symbol Parameter	Parameter			All peripherals enabled	All peripherals	Unit
		72MHz	20.52	12.19		
	Supply current		48MHz	14.71	9.13	
I_{DD}	I _{DD} in operating mode	Internal clock	36MHz	11.76	7.58	mA
			24MHz	6.158	1.544	
			8MHz	2.176	0.962	

1. The typical value is tested at T_A = 25°Cand V_{DD} = 3.3V.

Table 17. Typical current consumption in sleep mode, code executing from Flash or RAM

Symbol				Тур		
	Parameter	Conditions	f _{HCLK} ⁽²⁾	All peripherals enabled	All peripherals disabled	Unit
Supply current in sleep mode	Supply current		72MHz			
		Internal clock	48MHz	9.84	6.12	mA
	in sieep mode		8MHz	2.17	1.55	

- 1. The typical value is tested at T_A = 25°Cand V_{DD} = 3.3V.
- 2. External clock is 8MHz, when $f_{HCLK} > 8MHz$ choose HSI48 or HSI72.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in Table 18. The MCU is placed under the following conditions:

- All I/O pins are in analog input mode, and are connected to a static level —- V_{DD} or V_{SS} (no load).
- All peripherals are disabled except when explicitly mentioned.
- The given value is calculated by measuring the current consumption.
 - with all peripherals clocked OFF
 - with only one peripheral clocked on
- Ambient operating temperature and supply voltage conditions V_{DD} summarized in Table 12.

Table 18. On-chip peripheral current consumption⁽¹⁾

Perip	oheral	Typical consumption at 25 °C	Unit	Peripheral		Peripheral		Typical consumption at 25 °C	Unit
	HWDIV	2.17		APB2	SPI	7.92			
	GPIOD	0.75			TIM1	17.04			
	GPIOC	0.58	uA/MHz		ADC	1.54	uA/MHz		
AHB	GPIOB	0.71			SYSCFG	0.37			
	GPIOA	0.71			PWR	0.79			
	CRC	1.00			I2C	9.58			
	DMA	4.38			WWDG	5.96			
	PWM	1.75		APB1	TIM3	8.83			
ADD2	TIM17	3.29			TIM2	0.50			
APB2	TIM16	3.17			UART2	5.96	1		
	TIM14	3.17			UART2				

1. $f_{HCLK} = 72MHz$, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, the prescale coefficient for each device is the default value.

5.3.5 External clock source characteristics

High-speed external user clock generated from an external source

The characteristic parameters given in the following table are measured using a highspeed external clock source, ambient temperature and power supply voltage meet the conditions of General operating conditions.

Table 19. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	User external clock source		2	0	24	N41.1-
f_{HSE_ext}	frequency ⁽¹⁾		2	8	24	MHz
W	OSC_IN input pin high level		0.7V _{DD}		V	
V_{HSEH}	voltage	voltage	U.7 V _{DD}	V_{DD}	V	
	OSC_IN input pin low level		W		0.3V _{DD}	V
V_{HSEL}	voltage		V_{SS}		U.SV _{DD}	
$t_{w(HSE)}$	OSC_IN high or low time ⁽¹⁾		16			
$t_{r(HSE)}$	OSC IN rise or fall time ⁽¹⁾				20	nS
$t_{\sf f(HSE)}$	OOO_IIV HSC OF Idil time				20	
$C_{\text{in}(\text{HSE})}$	OSC_IN input capacitance ⁽¹⁾			5		pF
$DuCy_{(HSE)}$	Duty cycle		45		55	%
IL	OSC_IN input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$			±1	uA

1. Guaranteed by design, not tested in production.

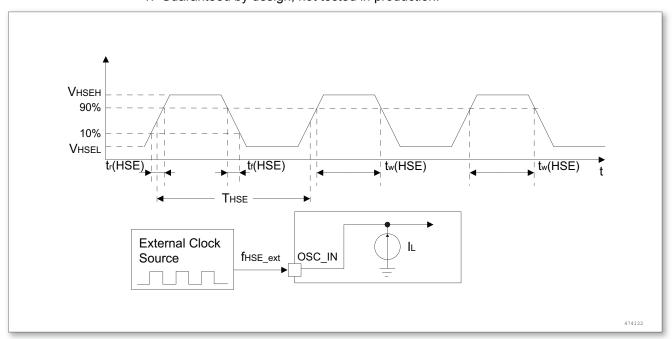


Figure 14. High-speed external clock source AC timing diagram

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with an 2 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in the table below. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy...).

Table 20. HSE oscillator characteristics (1)(2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency		2	8	24	MHz
R _F	Feedback resistor	$R_S = 30\Omega$		1000		kΩ
$\begin{array}{c} C_{L1} \\ C_{L2} ^{(3)} \end{array}$	The proposed load capacitance corresponds to the crystal serial impedance $\left(R_{S}\right)^{(4)}$	$V_{DD} = 3.3V$ $V_{IN} = V_{SS}$ 30pF load		30		pF
l ₂	HSE current consumption	Startup			4.5	mA
g _m	Oscillator transconductance	V _{DD} is stabilized		8.5		mA/V
t _{SU(HSE)} ⁽⁵⁾	Startup time	$R_S = 30\Omega$		2		mS

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer characteristics Parameter.
- 2. Guaranteed by design, not tested in production.
- 3. For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (Typ.) , designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .
- 4. The relatively low value of the RF resistance can be used to avoid problems arising from the use of wet conditions to provide protection, this environment resulting in leakage and bias conditions have changed. However, if the MCU is applied in bad wet conditions, the design needs to take this parameter into account.
- t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

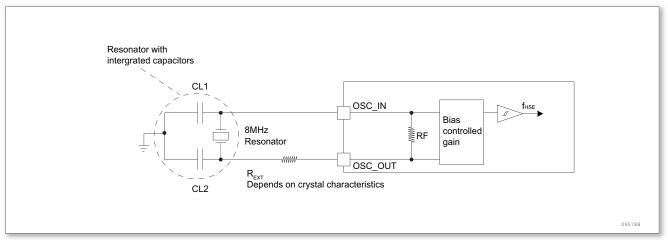


Figure 15. Typical application with an 8 MHz crystal

5.3.6 Internal clock source characteristics

The characteristic parameters given in the table below are measured using ambient temperature and supply voltage in accordance with general operating conditions.

High-speed internal (HSI) oscillator

Table 21. HSI oscillator characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI}	Frequency			72		MHz
ACC _{HSI}	Accuracy of the HSI oscillator	T _A = -40°C ~ 105°C	-3		3	%
ACC _{HSI}	Accuracy of the HSI oscillator	T _A = -10°C ~ 85°C	-2		2	%
ACC _{HSI}	Accuracy of the HSI oscillator	T _A = 0°C ~ 70°C	-1		1	%
ACC _{HSI}	Accuracy of the HSI oscillator	T _A = 25	-1		1	%
t _{SU(HSI)}	HSI oscillator startup time			10		μS
I _{DD(HSI)}	HSI oscillator power consumption			200		μA

- 1. V_{DD} = 3.3V, T_A = -40°C \sim 105°C, unless otherwise specified.
- 2. Guaranteed by design, not tested in production.

Low-speed internal (LSI) oscillator

Table 22. LSI oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSI} ⁽²⁾	Frequency		31	40	75	KHz
t _{SU(LSI)} (2)	LSI oscillator startup time				100	μS

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD(LSI)} (3)	LSI oscillator power			1 1	1.7	μA
	consumption			1.1	1.7	μΑ

- 1. V_{DD} = 3.3V, T_A = -40°C \sim 105°C, Unless otherwise stated
- 2. Comprehensive assessment, not tested in production.
- 3. Guaranteed by design, not tested in production.

Wake-up times from low power mode

The wake-up times listed in the table below are measured during the wake-up phase of the internal clock HSI. The clock source used when waking up depends on the current operating mode:

- · Stop or Standby mode: The clock source is the oscillator
- · Sleep mode: The clock source is the clock used when entering sleep mode

All times are measured using ambient temperature and supply voltage in accordance with common operating conditions.

Table 23. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Max	Unit
t _{WUSLEEP} (1)	Wakeup from Sleep mode	· HSI clock wakeup		μS
t _{WUSTOP} ⁽¹⁾	Wakeup from Stop mode	HSI clock wakeup < 2µS	12	μS
twustdby ⁽¹⁾	Wakeup from Standby mode	HSI clock wakeup < 2μS The regulator wakes up from the off mode < 30μS	230	μS

1. The wake-up time is measured from the start of the wake-up event to the user program to read the first instruction.

5.3.7 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40^{\circ}C \sim 105^{\circ}$ Cunless otherwise specified.

Table 24. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{prog}	8-bit programming time			6	7.5	μS
t _{ERASE}	Page (512K bytes) erase time			4	5	mS

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{ME}	Mass erase time			30	40	mS
	Supply current	Read mode		9		mA
I_{DD}		Write mode			7	mA
		Erase mode			2	mA
V _{prog}	Programming voltage			1.5		V

Table 25. Flash memory endurance and data retention⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Endurance					
	(Annotation:					
NEND	Erase		20			K cycle
	number of					
	times)					
4	Data	T _A = 105°C	20			Year
t _{RET}	retention	T _A = 25°C	100			Teal

- 1. Guaranteed by design, not tested in production.
- 2. Cycle tests are carried out in the whole temperature range.

5.3.8 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to VDD and VSS through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in the following table. They are based on the EMS levels and classes defined in application note.

Table 26. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
	Fast transientvoltage burst		
	limits to be applied through	$V_{DD} = 3.3V, T_A = +25^{\circ}C,$	
V_{EFT}	100 pF on V_{DD} and V_{SS}	f _{HCLK} =48MHz.Conformingto	2A
	pinsto induce a functional	IEC 1000-4-4	
	disturbance		

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors.

5.3.9 Absolute Maximum (Electrical Sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD78A IC latch-up standard.

Table 27. ESD characteristics

Symbol	Parameter	eter Conditions		Unit	
V	Electrostatic discharge voltage	$T_A = +25^{\circ}C$, Conforming to	6000		
$V_{ESD(HBM)}$	(Human body model)	JESD22-A114	8000	V	
	Electrostatic discharge voltage	T _A = +25°C, Conforming to	500		
$V_{ESD(CDM)}$	(Charging device model)	JESD22-C101	500		
	$T_A = +25^{\circ}C$, Conforming to		200	A	
I _{LU}	Latch-up current	JESD78A	200	mA	

5.3.10 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in Table 9 are derived from tests.

Table 28. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL} (Hysteresis open)	Low level input voltage	CMOS Port	0.16V _{DD}		0.2V _{DD}	V
V _{IH (Hysteresis open)}	High level input voltage	CMOS Port	0.8V _{DD}		0.84V _{DD}	V
V _{IL (Hysteresis close)}	Low level input voltage	CMOS Port	0.33V _{DD}		0.37V _{DD}	V
V _{IH (Hysteresis close)}	High level input voltage	CMOS Port	0.58V _{DD}		0.62V _{DD}	V
V _{hys (Hysteresis open)}	Schmitt trigger hysteresis ⁽¹⁾		1.2	3	3.3	V
V _{hys (Hysteresis close)}	Schmitt trigger hysteresis ⁽¹⁾		0.5	1.2	1.4	V
I _{Ikg}	Input leakage current(2)				±1	μΑ
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	V _{IN} = V _{SS}	28.7	36	47.9	k Ω
R _{PD}	Weak pull-down equivalent resistor ⁽³⁾	V _{IN} = V _{DD}	25	31.2	40	kΩ
C _{IO}	I/O pin capacitance			5		pF

- Schmitt Trigger switching hysteresis voltage level. Data based on design simulation only. Not tested in production.
- 2. The leakage could be higher than the maximum value, if negative current is injected on adjacent pins.

3. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (10% order).

All I/Os are CMOS (no software configuration required). Their characteristics cover more than the strict CMOS-technology.

- For V_{IH}:
 - If V_{DD} is between [2.50V \sim 3.08V]; use CMOS features.
 - If V_{DD} is between [3.08V \sim 3.60V]; include CMOS.
- For V_{IL}:
 - Use CMOS features.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±20mA.

n the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in 5.2:

- The sum of the currents obtained from V_{DD} for all I/O ports, plus the maximum operating current that the MCU obtains on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} .
- The sum of the currents drawn by all I/O ports and flowing out of V_{SS}, plus the maximum operating current of the MCU flowing out on V_{SS}, cannot exceed the absolute maximum rating I_{VSS}.

Output voltage levels

Unless otherwise stated, the parameters listed in the table below are measured using the ambient temperature and V_{DD} supply voltage in accordance with the condition of Table 12. All I/O ports are CMOS compatible.

Table 29. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL}	Output low level voltage for an I/O pin,when 8 pins absorb current	CMOS Port, I_{IO} = +8mA 2V < V_{DD} < 5.5V		0.4	V
V _{OH}	Output high level voltage for an I/O pin,when 8 pins output current	CMOS Port, I_{IO} = +8mA 2V < V_{DD} < 5.5V	V _{DD} -0.4		V
V _{OL}	Output low level voltage for an I/O pin,when 8 pins absorb current	I_{IO} = +20mA 2V < V_{DD} < 5.5V		0.4	V
V _{OH}	Output high level voltage for an I/O pin,when 8 pins output current	I_{IO} = +20mA $2V < V_{DD} < 5.5V$	V _{DD} -0.4		V

Input/output AC characteristics

The definitions and values of the input and output AC characteristics are given in figure 16 and Table 30, respectively.

Unless otherwise stated, the parameters listed in Table 30 are measured using the ambient temperature and supply voltage in accordance with the condition Table 9.

Table 30. I/O AC characteristics⁽¹⁾

out fi	Maximum requency ⁽²⁾ utput fall time	$C_L = 50 \text{pF},$ $V_{DD} = 2V \sim 5.5V$ $C_L = 50 \text{pF},$ $V_{DD} = 2V \sim 5.5V$		2 125	MHz
fi out Ot	utput fall time	$V_{DD} = 2V \sim 5.5V$ $C_{L} = 50pF,$ $V_{DD} = 2V \sim 5.5V$			
		V _{DD} = 2V ~ 5.5V		125	0
				125	
out Ou	Itput rise time	C = E0xE			nS
out Ou	ilpul iise liiile 🔠	$C_L = 50pF$,		125	
		V_{DD} = 2V ~ 5.5 V		125	nS
	Maximum	C _L = 50pF,		20	MHz
$f_{\text{max(IO)out}}$ frequency ⁽²⁾ $V_{\text{DD}} = 2V \sim 5.5V$		20	IVITIZ		
	ıtnut fall time	C _L = 50pF,		25	nS
out Ot	atput fail time	V_{DD} = 2V ~ 5.5		25	110
Ou	itnut rise time	$C_L = 50pF,$		25	nS
out Ou	itput rise time	V_{DD} = 2V ~ 5.5		25	110
Maxia		C _L = 30pF,		50	N 41 1-
out Maxin	num frequency (=)	V_{DD} = 2V ~ 5.5 V		30	MHz
Mayin	aum fraguanav(2)	$C_L = 50pF,$		30	MHz
)out MaxIII	num frequency	V_{DD} = 2V ~ 5.5 V		30	IVITZ
		$C_L = 30pF,$		5	nS
t OI	utput fall time	V_{DD} = 2V ~ 5.5 V		Ŭ.	110
idi.		$C_L = 50pF,$		8	nS
		V_{DD} = 2V ~ 5.5 V		, and the second	110
		$C_L = 30pF,$		5	nS
out Ou	Itput rise time	V_{DD} = 2V ~ 5.5 V		J	113
, at		$C_L = 50pF,$		8	nS
		V_{DD} = 2V ~ 5.5 V			113
Pulsa	width of external				
			10		nS
	-				
	out Ou out Ou out Ou out Ou out Ou out Ou pout Maxin out Ou pout Ou Pulse signal	Output fall time Output rise time Output Maximum frequency(2) Output Maximum frequency(2) Out Output fall time	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

- 1. The speed of the I/O port can be configured via MODEx[1:0]. See the description of the GPIO Port Configuration Register in this chip reference manual.
- 2. The maximum frequency is defined in figure 16.

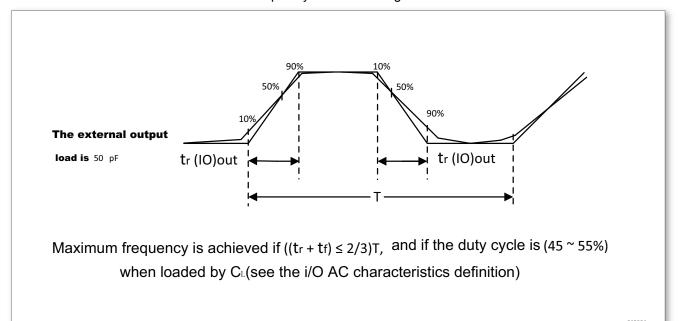


Figure 16. I/O AC characteristics

5.3.11 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pullup resistor, R_{PU} .

Unless otherwise stated, the parameters listed in the table below are measured using the ambient temperature and V_{DD} supply voltage in accordance with the condition of Table 12.

Table 31. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage		-0.5		0.8	V
V _{IH(NRST)} ⁽¹⁾	NRST input high level voltage		2		V_{DD}	V
$V_{\text{hys}(\text{NRST})}$	NRST Schmitt trigger voltage hysteresis			0.2V _{DD}		V
R _{PU}	Weak pull-up equivalent resistor ⁽²⁾	V _{IN} = V _{SS}		50		kΩ
V _{NF(NRST)} ⁽¹⁾	NRST input not filtered pulse		300			ns

- 1. Data based on design simulation only. Not tested in production.
- 2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (10% order).

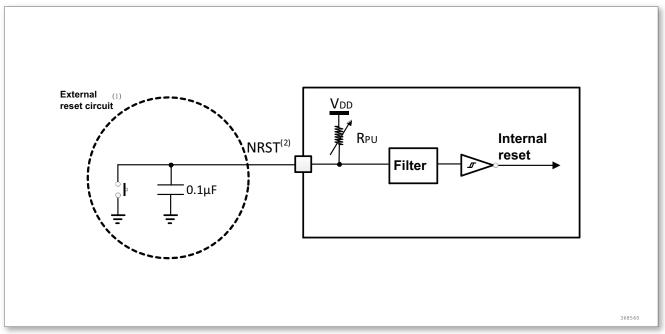


Figure 17. Recommended NRST pin protection

- 1. The reset network is to prevent parasitic reset
- 2. The user must ensure that the potential of the NRST pin is below the maximum $V_{\text{IL}(\text{NRST})}$ listed in Table 31, otherwise the MCU cannot be reset.

5.3.12 Timer characteristics

The parameters given in the following tables are guaranteed by design.

For details on the characteristics of the I/O multiplexing function pins (output compare, input capture, external clock, PWM output), see subsubsec 5.3.10.

Table 32. TIMx⁽¹⁾ characteristics

Symbol	Parameter	Conditions	Min	Max	Unit	
t _{res(TIM)}	Timer resolution time		1		t _{TIMxCLK}	
$t_{res(TIM)}$	Timer resolution time	f _{TIMxCLK} = 72MHz	10.4		nS	
f	Timer external clock		0	f _{TIMxCLK}	MHz	
f _{EXT}	frequency on CH1 to CH4	f _{TIMxCLK} = 72MHz	0	72	IVII IZ	
Res _{TIM}	Timer resolution			16	Bit	
4	16-bit timer		1	65536	t _{TIMxCLK}	
tcounter	maximum period	f _{TIMxCLK} 72MHz	0.0139	910	μS	
+	The maximum possible count			65536 × 65536	t _{TIMxCLK}	
t _{MAX_COUNT}	The maximum possible count	f _{TIMxCLK} 72MHz		59.6	S	

1. TIMx is a generic name, representing TIM1,2,3,14,16,17.

5.3.13 Communication interfaces

I2C interface characteristics

Unless otherwise specified, the parameters given in Table 33 are derived from tests performed under the ambient temperature, f_{PCLK1} frequency and supply voltage conditions summarized in Table 12: General operating conditions.

The I2C interface conforms to the standard I2C communication protocol, but has the following limitations: SDA and SCL are not true pins. When configured as open-drain output, the PMOS transistor between the pin and V_{DD} Was closed but still exists.

The I2C I/Os characteristics are listed in Table 33, the alternate function characteristics of I/Os (SDA and SCL) refer to subsubsec 5.3.10.

Table 33. I2C characteristics

O b l	Davision	Standard I2C ⁽¹⁾		Fast I2C (1)(2)		I I m i 4
Symbol	Parameter	Min	Max	Min	Max	Unit
t _{w(SCLL)}	SCL clock fall time	4.7		1.3		μS
t _{w(SCLH)}	SCL clock rise time	4.0		0.6		μS
t _{su(SDA)}	SDA setup time	250		100		
t _{h(SDA)}	SDA data hold time	0(3)		0(4)	900(3)	no
$t_{r(SDA)} t_{r(SDL)}$	SDA and SCL rise time		1000	2.0+0.1C _b	300	ns
$t_{f(SDA)} t_{f(SDL)}$	SDA and SCL fall time		300		300	
t _{h(STA)}	Start condition hold time	4.0		0.6		
t _{su(STA)}	Start condition setup time	4.7		0.6		
t _{su(STO)}	Stop condition setup time	4.0		0.6		μ\$
t _{w(STO:STA)}	Time from Stop condition to	4.7		4.0		
	Start condition	4.7		1.3		
C _b	Capacitive load of each bus		400		400	pF

- 1. Guaranteed by design, not tested in production.
- 2. f_{PCLK1}must be at least 3MHz to achieve standard mode I2C frequencies. It must be at least 12MHz to achieve fast mode I2C frequencies.
- 3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.
- 4. In order to span the undefined area of the falling edge of SCL, it must ensure that the SDA signal has a hold time of at least 300nS.

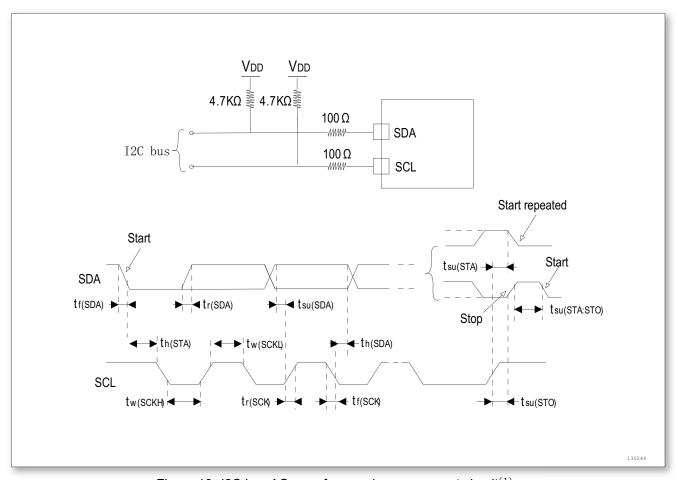


Figure 18. I2C bus AC waveform and measurement circuit⁽¹⁾

1. Measurement point is set to the CMOS level: $0.3V_{DD}$ and $0.7V_{DD}$.

SPI characteristics

Unless otherwise specified, the parameters given in Table 34 are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in Table 12.

Refer to subsubsec 5.3.10 for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 34. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f 1/t	CDI alook froguanay	Master mode	0	36	MHz
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	ck frequency Slave mode		18	IVITIZ
$t_{\text{r}(\text{SCK})}$	SPI clock rise and fall	Load capacitance: C = 30pF		8	ns
$t_{\text{f}(\text{SCK})}$	time	Load capacitatice. C - 30pr		0	115
$t_{su(NSS)}^{(2)}$	NSS setup time	Slave mode	4t _{PCLK}		ns
$t_{h(\text{NSS})}^{)}(2)}$	NSS hold time	Slave mode	73		ns

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{w(SCKL)}^{(2)}$ $t_{w(SCKL)}^{(2)}$	SCK high and low time	Master mode, f _{PCLK} = 36MHz, prescale coefficient = 4	50	60	ns
$t_{su(SI)}^{(2)}$	Data input setup time, Slave mode		1		ns
$t_{h(SI)}^{(2)}$	Data input hold time, Slave mode		3		ns
$t_{a(SO)}^{(2)(3)}$	Data output access time	Slave mode, f _{PCLK} = 36MHz, prescale coefficient = 4 Slave mode, f _{PCLK} = 24MHz	0	55 4t _{PCLK}	
t _{dis(SO)} (2)	Data output disable time	Slave mode	10		-
$t_{v(SO)}^{(2)(1)}$	Data output valid time	Slave mode (after enable edge)		25	ns
$t_{v(MO)}^{(2)(1)}$	Data output valid time	Master mode (after enable edge)		3	
$t_{h(SO)}^{(2)}$	Data output hold time	Slave mode (after enable edge)	25		
$t_{h(MO)}^{(2)}$	Data output hold time	Master mode (after enable edge)	4		

- 1. Data based on characterization results. Not tested in production.
- 2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
- 3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

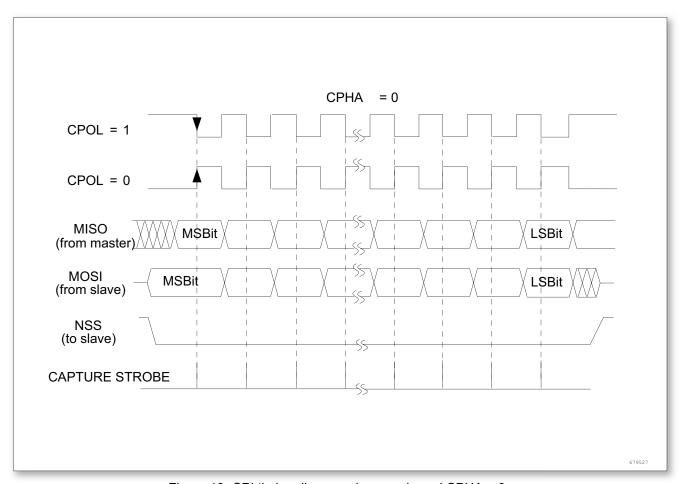


Figure 19. SPI timing diagram-slave mode and CPHA = 0

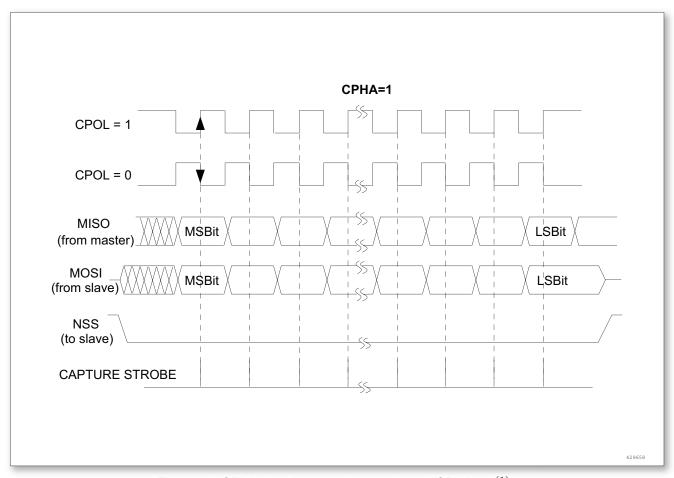


Figure 20. SPI timing diagram-slave mode and CPHA = $\mathbf{1}^{(1)}$

1. Measurement points are done at CMOS levels: $0.3\mbox{V}_{\mbox{\scriptsize DD}}$ and $0.7\mbox{V}_{\mbox{\scriptsize DD}}.$

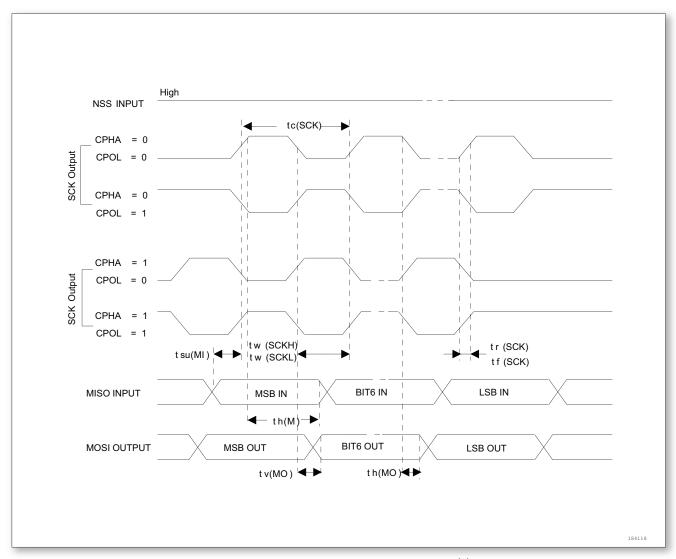


Figure 21. SPI timing diagram-master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

5.3.14 12-bit ADC characteristics

Unless otherwise specified, The parameters in the table below are measured using the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage in accordance with the conditions of Table 12.

Note: It is recommended to perform a calibration after each power-up

Table 35. ADC characteristics

Symbol	Parameter	Conditions	Min	Туре	Max	Unit
V_{DDA}	Supply voltage		2.0	3.3	5.5	V
V_{REF+}	Positive reference voltage		2.0		V_{DDA}	V

Symbol	Parameter	Conditions	Min	Туре	Max	Unit
f _{ADC}	ADC clock frequency				15 ⁽¹⁾	MHz
f _S ⁽²⁾	Sampling rate				1	MHz
f _{TRIG} (2)	External trigger frequency	f _{ADC} = 15MHz			823 1/17	KHz 1/f _{ADC}
$V_{AIN}^{(2)}$	Conversion voltage		0 (V _{SSA} or V _{REF} -connected to ground)		V_{REF^+}	V
R _{AIN} ⁽²⁾	External sample and hold capactor		See For	mulas 1 and Ta	ble 36	kΩ
R _{ADC} ⁽²⁾	Sampling switch resistance				1	kΩ
C _{ADC} ⁽²⁾	Internal sample and hold capacitor			10		pF
t _S (2)	Sampling time	f _{ADC} = 15MHz	0.1 1.5		16 239.5	μS 1/f _{ADC}
t _{STAB} (2)	Stabilization time			1		μS
	Total conversion	f _{ADC} = 15MHz	1		16.9	μS
t _{conv} (2)	time (including Sampling time)			sampling t_{S^+}) so proximation 13.	·	1/f _{ADC}

- 1. Guaranteed based on test during characterization. Not tested in production.
- 2. Guaranteed by design. Not tested in production.
- 3. In this series of products, V_{REF+} is internally connected to $_{DDA}$, V_{REF-} is internally connected to $_{SSA}$.

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times In(2^{N+2})} - R_{ADC}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 36. Maximum R_{AIN} at f_{ADC} = 15MHz⁽¹⁾

T _S (cycles)	t _S (μs)	\mathbf{R}_{AIN} max ($k\Omega$)
1.5	0.1	1.2
7.5	0.5	30
13.5	0.9	57
28.5	1.9	123
41.5	2.76	180
55.5	3.7	240

T _S (cycles)	t _S (μs)	\mathbf{R}_{AIN} max (k Ω)
71.5	4.77	312
239.5	16.0	1050

1. Guaranteed by design. Not tested in production.

Table 37. ADC Accuracy - Limit Test Conditions (1)(2)

Symbol	Parameter	Test Conditions	Туре	Max	Unit
ET	Comprehensive error		±10	±14	
EO	Offset error	$f_{PCLK2} = 60MHz, f_{ADC} =$	±4	±10	
EG	Gain error	$15MHz,R_{AIN} < 10K\Omega,V_{DDA}$	±6	±8	LSB
ED	Differential linearity error	= 5V,T _A = 25°C	±2	±4	
EL	Integral linearity error		±4	±6	

- 1. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
 - Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in subsubsec 5.3.11 does not affect the ADC accuracy.
- 2. Guaranteed based on test during characterization. Not tested in production.

ET = Total unadjusted error: The maximum deviation between the actual and ideal transmission curves.

EO = Offset error: The deviation between the first actual conversion and the first ideal conversion.

EG = Gain error: The deviation between the last ideal transition and the last actual transition.

ED = Differential linearity error: The maximum deviation between the actual step and the ideal value.

EL = Integral linearity error: The maximum deviation between any actual conversion and the associated line of the endpoint.

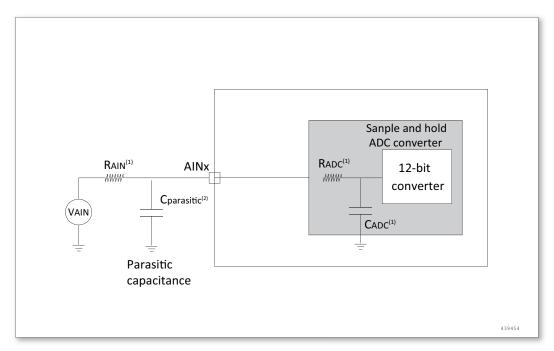


Figure 22. Typical connection diagram using the ADC

- 1. See Table 37 for the values of R_{AIN} , R_{ADC} and C_{ADC} .
- 2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

PCB design recommendations

The power supply must be connected as shown below. The 10nFcapacitor in the figure must be a ceramic capacitor (good quality), and they should be as close as possible to the MCU chip.

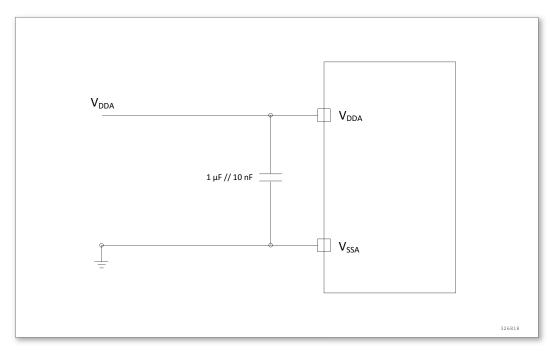


Figure 23. Power supply and reference power supply decoupling circuit

5.3.15 Temperature sensor characteristics

Table 38. Temperature sensor characteristics (3)(4)

Symbol	Parameter	Min	Туре	Max	Unit
T _L ⁽¹⁾	V _{SENSE} linearity with respect to		ı.E		°C
I L ()	temperature		±5		
Avg_Slope ⁽¹⁾	Average slope	4.571	4.801	5.984	mV/°C
$V_{25}^{(1)}$	Voltage at 25°C	1.433	1.451	1.467	V
t _{start} (2)	Setup time			10	μs
T (2)	ADC sampling time when	10			0
$T_{S_temp}^{(2)}$	reading temperature	10			μS

- 1. Guaranteed based on test during characterization. Not tested in production.
- 2. Guaranteed by design. Not tested in production.
- 3. The shortest Sampling time can be determined by the application through multiple iterations.
- 4. $V_{DD} = 3.3V$.

5.3.16 Comparator characteristics

Table 39. Comparator characteristics

Symbol	Parameter	Register configuration	Min	Туре	Max	Unit
HYST	Hysteresis	00		0		mV
HYST	Hysteresis	01		15		mV
HYST	Hysteresis	10		30		mV

Symbol	Parameter	Register configuration	Min	Туре	Max	Unit
HYST	Hysteresis	11		90		mV
OFFSET	Offset voltage	00	0.091	0.213	0.358	mV
OFFSET	Offset voltage	01	3.23	7.51	12.08	mV
OFFSET	Offset voltage	10	9.79	15	20.8	mV
OFFSET	Offset voltage	11	34.25	47.4	62.22	mV
DELAY ⁽¹⁾	Propagation delay	00		80		nS
DELAY ⁽¹⁾	Propagation delay	01		51		nS
DELAY ⁽¹⁾	Propagation delay	10		26		nS
DELAY ⁽¹⁾	Propagation delay	11		9		nS
$I_q^{(2)}$	Operating current mean	00		4.5		uA
$I_q^{(2)}$	Operating current mean	01		4.4		uA
$I_q^{(2)}$	Operating current mean	10		4.4		uA
$I_q^{(2)}$	Operating current mean	11		4.4		uA

- 1. The output flips 50% of the time and the time difference between the input and the flip.
- 2. Total current consumption, operating current.

6

Package information

Package information

6.1 LQFP48 Package information

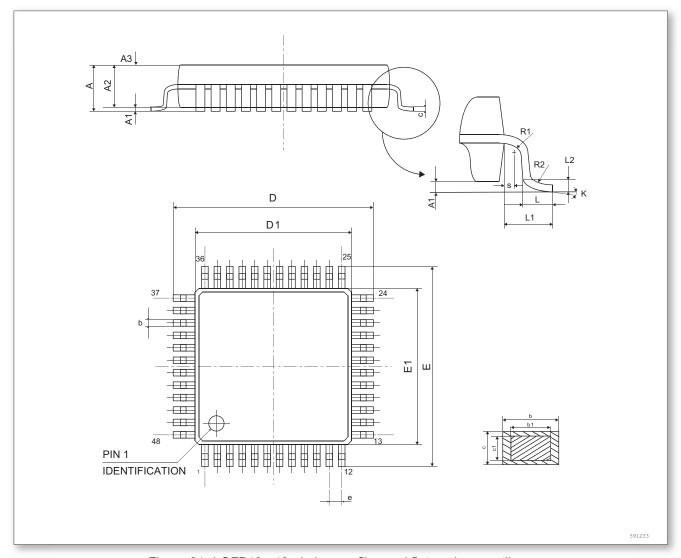


Figure 24. LQFP48 - 48-pin low-profile quad flat package outline

- 1. Drawing is not to scale.
- 2. Dimensions are expressed in millimeters.

Table 40. LQFP48 mechanical data

O		Millimeters	
Symbol	Min	Тур	Max
A			1.60
A1	0.05		0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
b	0.18		0.27
b1	0.17	0.20	0.23
С	0.13		0.18
c1	0.12	0.127	0.134
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
E	8.80	9.00	9.20
E1	6.90	7.00	7.10
е		0.50	
L	0.45	0.60	0.75
L1		1.00REF	
L2		0.25BSC	
R1	0.08		
R2	0.08		0.20
S	0.20		
N		Number of pins = 48	<u> </u>

6.2 LQFP32 Package information

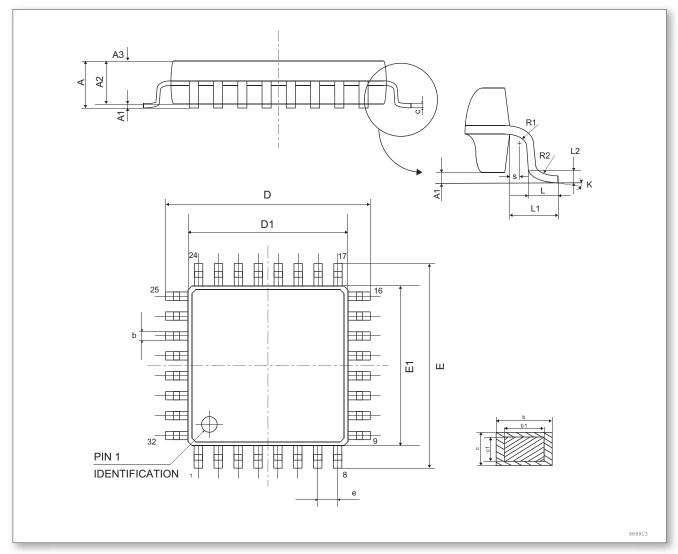


Figure 25. LQFP32 - 32-pin low-profile quad flat package outline

- 1. Drawing is not to scale.
- 2. Dimensions are expressed in millimeters.

Table 41. LQFP32 mechanical data

Symbol		Millimeters	
Symbol	Min	Тур	Max
A			1.60
A1	0.05		0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
b	0.32		0.43
b1	0.31	0.35	0.39
С	0.13		0.18
c1	0.12	0.127	0.134

Occurate at		Millimeters				
Symbol	Min	Тур	Max			
D	8.80	9.00	9.20			
D1	6.90	7.00	7.10			
E	8.80	9.00	9.20			
E1	6.90	7.00	7.10			
е		0.80				
L	0.45	0.60	0.75			
L1		1.00REF				
L2		0.25BSC				
R1	0.08					
R2	0.08		0.20			
S	0.20					
N		Number of pins = 32				

6.3 QFN32 Package information

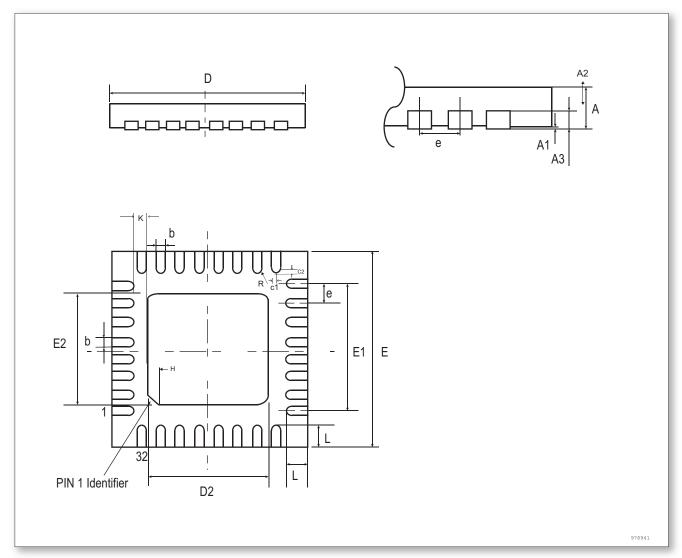


Figure 26. QFN32 - 32-pin quad flat no-leads package outline

- 1. Drawing is not to scale.
- 2. Dimensions are expressed in millimeters.

Table 42. QFN32 mechanical data

Symbol		Millimeters	
Symbol	Min	Тур	Max
А	0.7	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3		0.20REF	
b	0.20	0.25	0.30
D	4.90	5.00	5.10
Е	4.90	5.00	5.10
D2	3.40	3.50	3.60

Ol	Millimeters			
Symbol	Min	Тур	Max	
E2	3.40	3.50	3.60	
е		0.5		
Н		0.30REF		
K	0.35REF			
L	0.35	0.40	0.45	
R	0.09			
c1		0.08		
c2		0.08		
N		Number of pins = 32		

6.4 QFN20 Package information

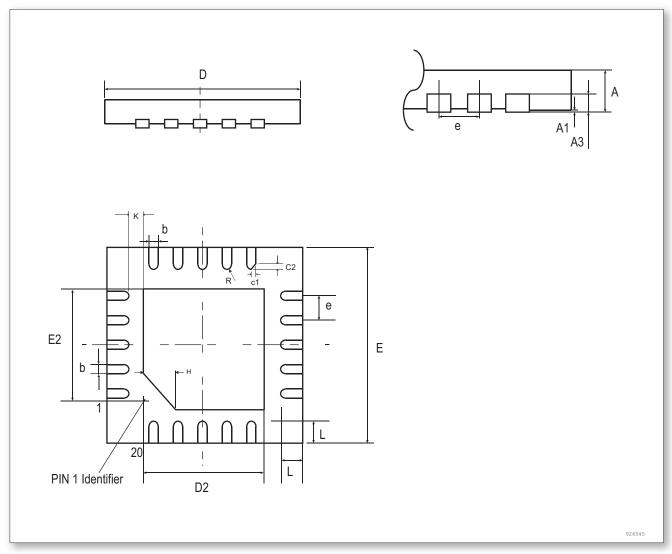


Figure 27. QFN20 - 20-pin quad flat no-leads package outline

- 1. Drawing is not to scale.
- 2. Dimensions are expressed in millimeters.

Table 43. QFN20 mechanical data

Symbol	Millimeters		
	Min	Тур	Max
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A3	0.152REF		
b	0.15	0.20	0.25
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.40	1.50	1.60
E2	1.40	1.50	1.60

Symbol	Millimeters		
	Min	Тур	Max
е		0.40	
Н		0.35REF	
K	0.40REF		
L	0.25	0.35	0.45
R	0.075		
N	Number of pins = 20		

6.5 TSSOP20 Package information

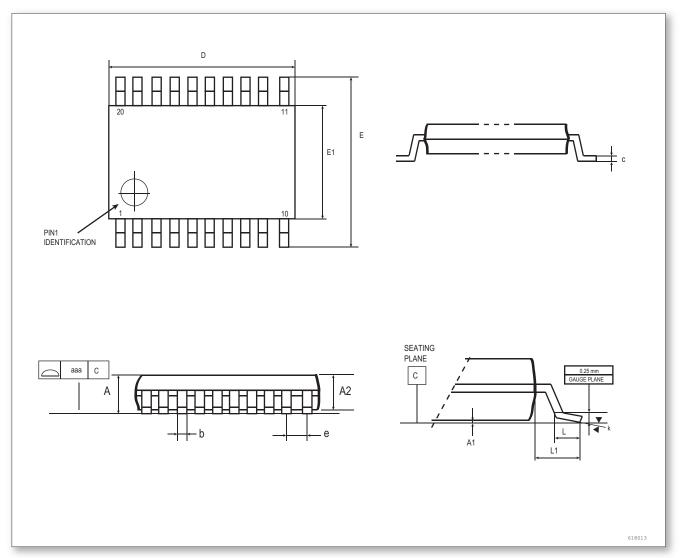


Figure 28. TSSOP20 - 20-lead thin shrink small outline package outline

- 1. Drawing is not to scale.
- 2. Dimensions are expressed in millimeters.

Table 44. TSSOP20 mechanical data

Symbol	Millimeters		
	Min	Тур	Max
A			1.20
A1	0.05		0.15
A2	0.8	1.00	1.05
b	0.19		0.30
С	0.09		0.20
D	6.40	6.50	6.60
Е	6.25	6.40	6.55
E1	4.30	4.40	4.50

Symbol	Millimeters		
	Min	Тур	Max
е		0.65	
L	0.45	0.60	1
L1	0.45		0.75
N		Number of pins = 20	

7

Ordering information

Ordering information

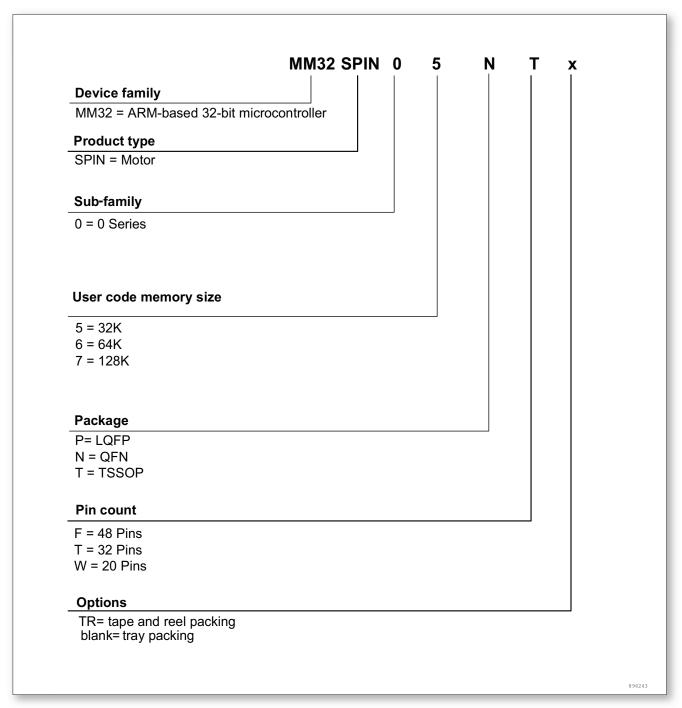


Figure 29. Ordering information scheme

8

Revision history

Revision history

Table 45. Document revision history

Revision	Changes	Date
Rev1.09	Modify the package parameters.	2019/3/11
Rev1.08	Modify the package parameters.	2019/3/6
Rev1.07	Add the QFN20 package.	2019/1/10
Rev1.05	Modify ADC electrical parameters.	2018/12/14
Rev1.04	Modify parameters.	2018/11/13
Rev1.03	Modify parameters.	2018/11/12
Rev1.02	Modify electrical parameters.	2018/10/11
Rev1.01	Modify pin definition.	2018/8/26
Rev1.00	Initial release.	2018/8/4